

Design of active bridge line rectification for SMPS

About this document

Scope and purpose

This document is an application note describing the design and operation of active bridge line rectification. It helps readers understand and build an active bridge line rectification device more easily. Moreover, it illustrates voltage and current waveforms in normal and burst mode operations of PFC to explain the activation function required for active bridge rectification under burst mode operation in a power supply. This application note proposes simple formulas to calculate power losses in bridge rectifiers and MOSFETs for estimating the total efficiency improvements in power supplies. Looking at the package outline, it compares MOSFETs based on $R_{DS(on)}$ package area and package volume. Reference boards with MOSFETs in various packages provide a visual concept to estimate space occupation. System solutions and a bridge rectifier are necessary to prevent active bridge line rectification MOSFETs from being damaged by overvoltage and over-current in a lightning surge test to IEC-61000-4-5, and under abnormal test, like AC cycle drop-out. Efficiency test results and a reference schematic are provided to demonstrate active bridge line rectification performance.

Intended audience

This document is intended for power supply designers, application engineers, students and anyone who wants to quickly improve the whole power range efficiency of a SMPS to achieve higher efficiency, such as that offered by 80 PLUS Titanium, or to improve the thermal status of power devices in high power density power supply units.

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1 Efficiency improvement with active bridge line rectification

1.1 Efficiency requirements

It is well known fact that efficiency and high power density are important in SMPS design. A variety of efficiency requirements, such as 80 PLUS or EuP, are defined for various SMPS. However, the product must also meet specifications, otherwise it may not be allowed to be sold in some markets.

Table 1 indicates the 80 PLUS efficiency requirements for non-redundant internal power supplies.

Table 1 80 PLUS efficiency requirements classification

80 PLUS efficiency requirement	115 V internal non-redundant (percent)				230 V internal non-redundant (percent)			
	10	20	50	100	10	20	50	100
80 PLUS		80	80	80				
80 PLUS Bronze		82	85	82		81	85	81
80 PLUS Silver		85	88	85		85	89	85
80 PLUS Gold		87	90	87		88	92	88
80 PLUS Platinum		90	92	89		90	94	91
80 PLUS Titanium	90	92	94	90	90	94	96	91

In addition to 80 PLUS, some customers define similar but stricter efficiency requirements based on system operation conditions. For example, as shown in [Figure 1](#), in 80 PLUS Platinum requirements, the efficiency requirements at 20 percent and 50 percent of rated loads are at 90 percent and 94 percent respectively. Customer A redefines the efficiency requirement of 94 percent from 20 percent to 70 percent of rated power. Even when the efficiency requirement is still 94 percent at 50 percent of rated power, efficiency results from a real test indicate 95 percent at 50 percent of rated power in order to fulfill the 94 percent efficiency requirement at 20 percent of rated power.

These standards define efficiency requirements at an input voltage of 230 V AC; however, some customers define the same efficiency requirements at 180 V AC, which in turn increases the efficiency requirements at 230 V AC. Besides, different customers define different efficiency requirements, from light load to full load, as their only system requirement. As a result, any effective method that is able to improve the efficiency of the whole power range will be quite attractive for power supply designers.

Efficiency improvement with active bridge line rectification

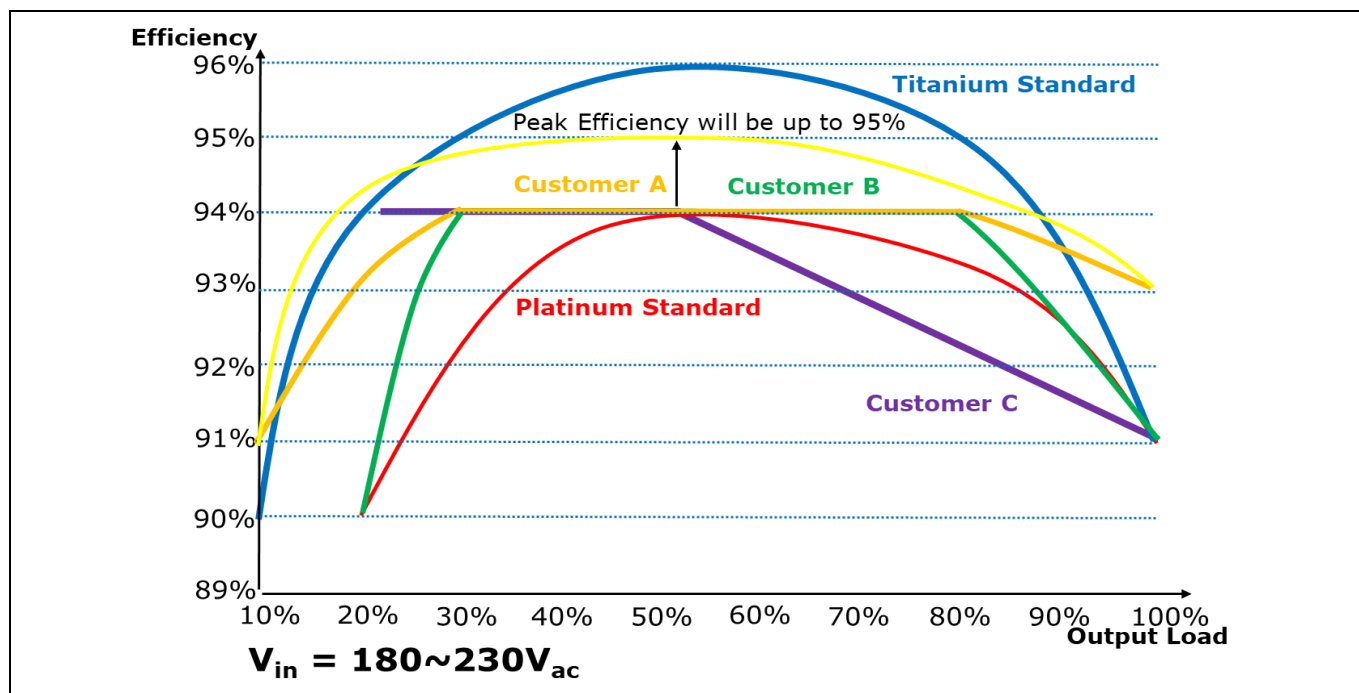


Figure 1 Standards and customized efficiency requirements for a redundant power supply

1.2 Efficiency improvement by reducing power loss on the bridge rectifier

A SMPS, with traditional PFC and highly efficient DC-DC converter, can intuitively meet the 80 PLUS Platinum efficiency requirements. In order to achieve a higher efficiency, such as 80 PLUS Titanium, maintaining the same circuit structure but adding efficiency improvements will not suffice. By only replacing the power components with better ones, like a MOSFET with lower $R_{DS(on)}$ or an inductor with less core material loss, it is almost impossible to achieve sufficient efficiency improvements.

Figure 2 shows the power dissipation of power devices in a 1000 W traditional PFC circuit. The bridge rectifier's power dissipation dominates among power devices, regardless of low-line or high-line input voltage. Reducing the power dissipation of a bridge rectifier is the most effective way to improve efficiency.

In order to reduce the power dissipation generated by the bridge rectifier, several bridgeless PFC topologies have been developed, as shown in **Figure 3**.

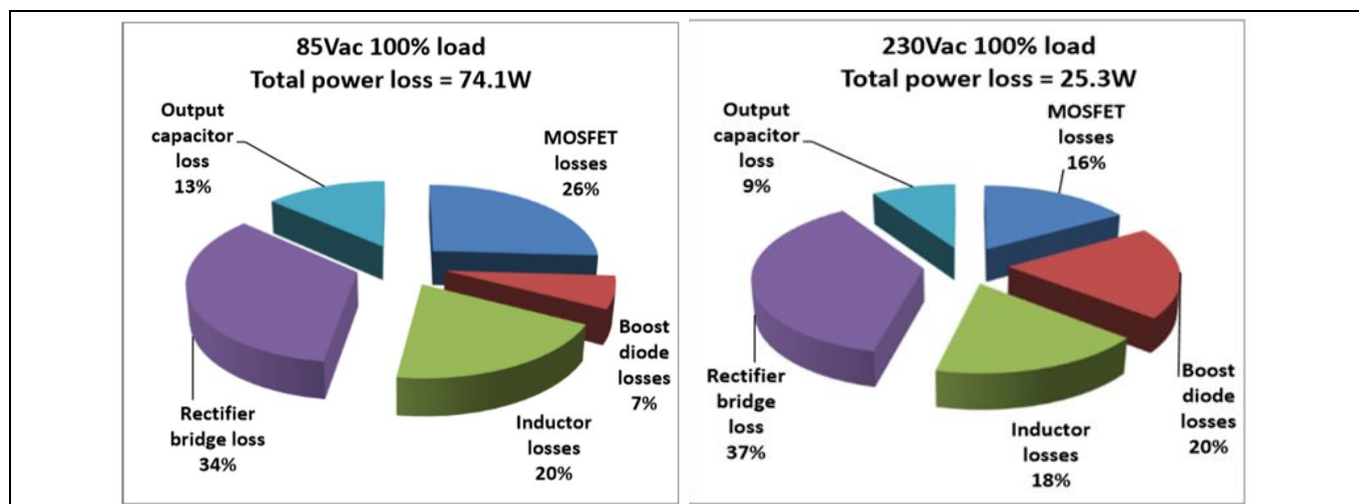


Figure 2 Power dissipation of power devices with a 1000 W PFC circuit at 85 V AC and 230 V AC

Efficiency improvement with active bridge line rectification

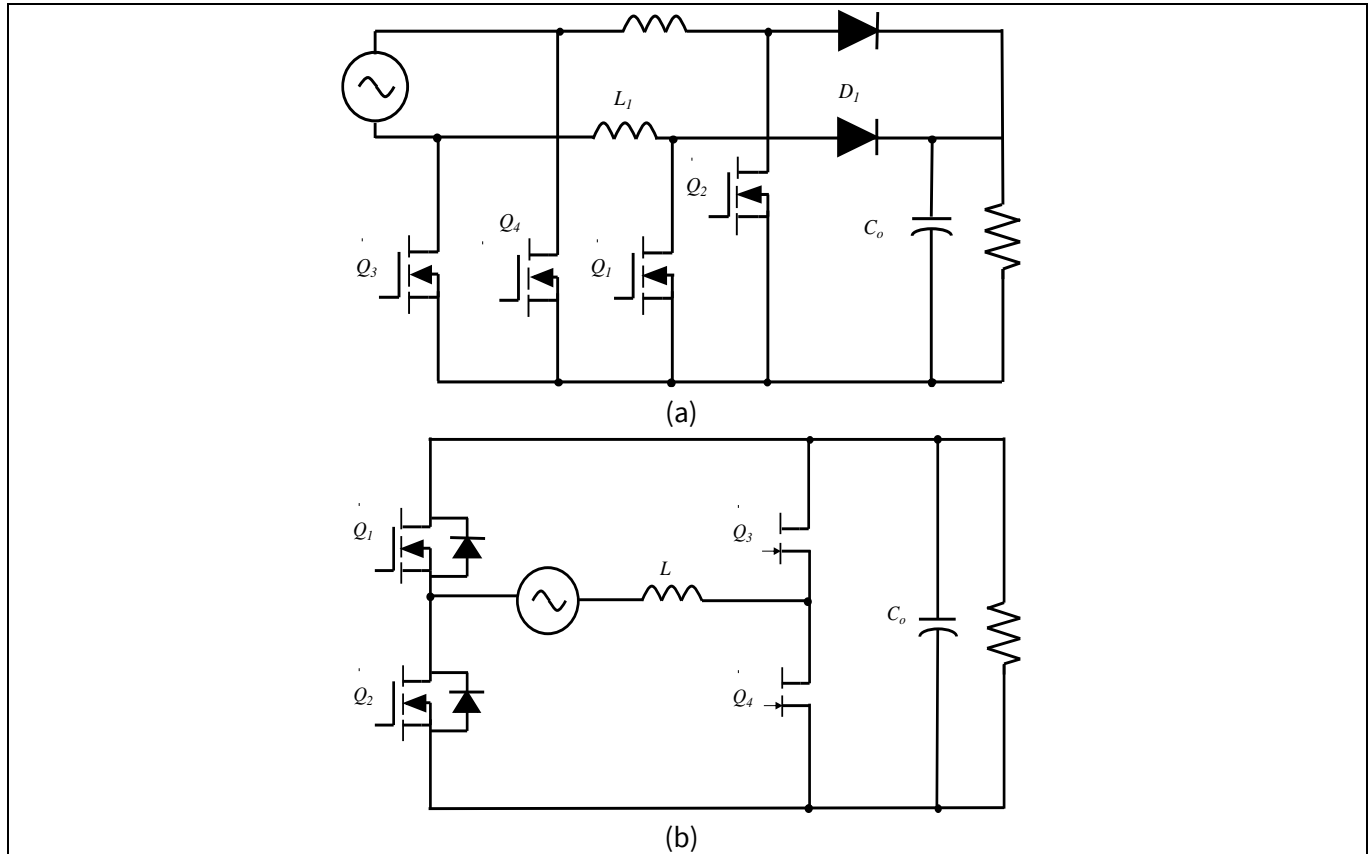


Figure 3 (a) Dual-boost bridgeless PFC circuit; (b) totem-pole bridgeless PFC

1.2.1 (a) Dual-boost bridgeless PFC circuit

A dual-boost bridgeless PFC combines two interleaved classic PFC circuits with two MOSFETs, Q_3 and Q_4 , shown in [Figure 3\(a\)](#), as return paths for positive and negative AC cycles respectively. The control method of a dual-boost bridgeless PFC is equal to a classic PFC circuit with a classic PFC controller. Each boost PFC stage in the dual-boost bridgeless PFC operates at positive and negative AC voltage cycles.

However, two power stages requiring dual-boost bridgeless PFC circuits makes it difficult to meet high power density requirements in most SMPS.

1.2.2 (b) Totem-pole bridgeless PFC circuit

A totem-pole bridgeless PFC, illustrated in [Figure 3\(b\)](#), is composed of one inductor, two switching MOSFETs (Q_3 and Q_4) and return MOSFETs (Q_1 and Q_2); it is therefore easier to achieve high power density than with a dual-boost bridgeless PFC. Considering the body diode conduction of both switching MOSFETs, wide-bandgap MOSFETs like GaN or SiC MOSFETs are inevitably used as switching MOSFETs in this topology. On the other hand, the control method in totem-pole PFCs means it is complicated to operate the MOSFET Q_3 as a switching MOSFET and MOSFET Q_4 as a synchronous freewheeling MOSFET at a positive AC polarity voltage cycle, but inversely at a negative AC cycle. Moreover, another challenge from the single inductor of the totem-pole PFC circuit is full duty-cycle operation near the AC zero-crossing area, but the inductor current direction should be inversed as input voltage crossing zero voltage from positive to negative or vice versa. Suitable duty-cycle control near the AC zero-crossing area is necessary to avoid the inductor's current spikes deteriorating the PF value and Total Harmonic Distortion (THD). Hence, as the controller, an MCU with AC voltage level and polarity detection is necessary in a totem-pole bridgeless PFC used for high-end power supplies, such as server power or telecom power.

Efficiency improvement with active bridge line rectification

In addition to the MCU and the complicated control, an auxiliary power circuit with a low standby power dissipation is necessary to power the internal controllers in the above two bridgeless PFC circuits. However, for some applications such as high power density adapters, constraints from topology, space, power-saving requirements and thermal considerations make it impossible to use the above two bridgeless PFC circuits. Active bridge line rectification then becomes a possible alternative solution for improving the efficiency and temperature of power supplies.

1.2.3 (c) Active bridge line rectification

An active bridge line rectification with PFC circuit is illustrated in **Figure 4**. It is implemented by paralleling low $R_{DS(on)}$ of MOSFETs with a bridge rectifier to reduce the conduction loss of the forward voltage of the bridge rectifier. For effective efficiency improvements, the product of the current and MOSFET $R_{DS(on)}$ should be lower than the forward voltage of the bridge rectifier even in a high current.

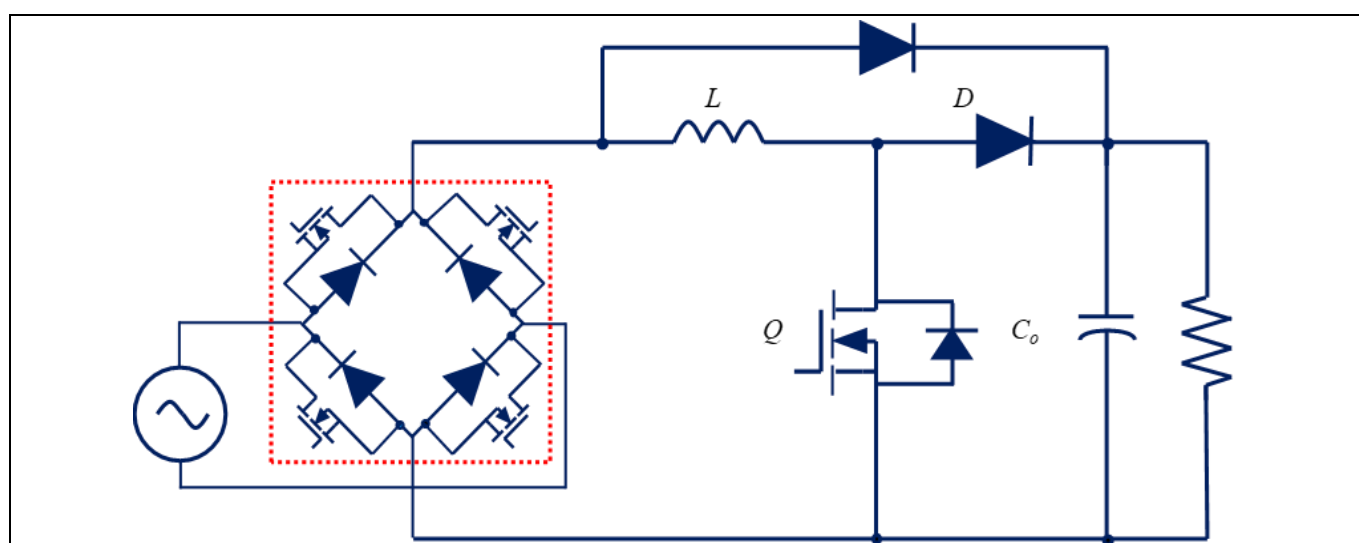


Figure 4 Active bridge line rectification with PFC circuit

Figure 5 shows an example of a 950 W industrial power supply, tested with an active bridge line rectification of 22 mΩ and 65 mΩ MOSFETs in a TOLL package at an AC voltage of 115 V. The efficiency is improved by 0.9 percent with an active bridge line rectification of 22 mΩ MOSFET at half load and full load. That is improved by 0.5 percent and 0.4 percent with an active bridge line rectification of 65 mΩ MOSFET at half load and full load respectively.

Efficiency improvement with active bridge line rectification

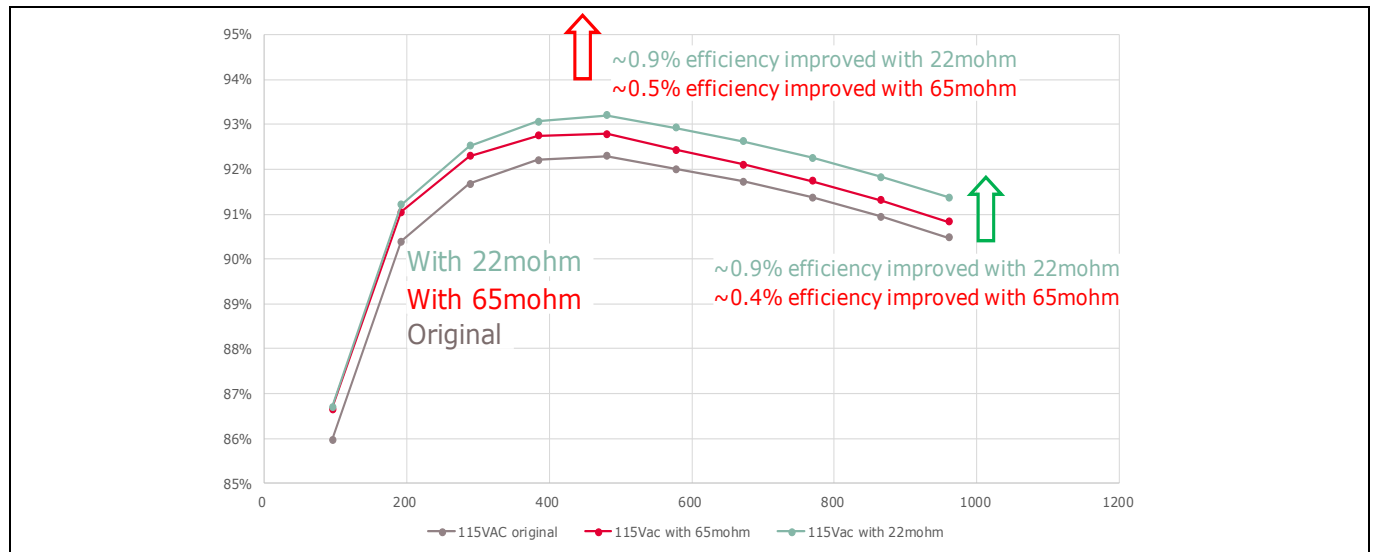


Figure 5 Efficiency test result of a 950 W industrial power supply with 22 mΩ and 65 mΩ full-wave active bridge line rectification

2 Control method for active bridge line rectification

2.1 Control concept for active bridge line rectification

The control concept for active bridge line rectification is intuitive. The control signal for each MOSFET of active bridge line rectification is obtained by comparing the divided instantaneous input voltage to a reference voltage, as shown in [Figure 5](#). It is obvious that the voltage divider resistance should be high to minimize the quiescent loss, especially in high-line input. The on-time control signal at each cycle depends on the input voltage level, which means shorter on-time is obtained at low-line input and vice versa. In general, at least 40 percent of duty-cycle control signals are obtained at a 115 V AC input voltage with line frequency.

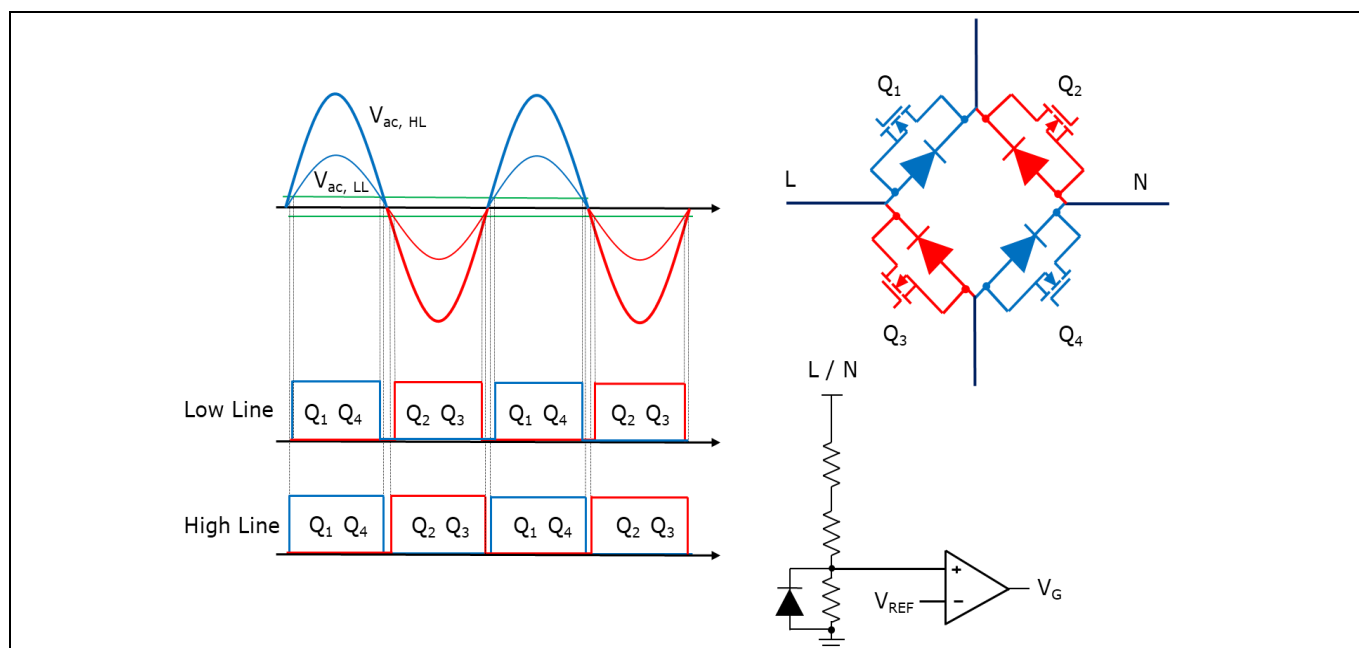


Figure 6 Control concept for active bridge line rectification

In a classic PFC circuit, the filter capacitor C_F connected to the rectified voltage “+” and reference GND “-” pin of a bridge rectifier causes zero cross-current distortion and worse PFC THD at light load. The discontinuous current is derived from the off-state of a bridge rectifier at a low-input instantaneous voltage and a higher rectified voltage of the filter capacitor at light load conditions.

However, a new current distortion waveform is observed when using active bridge line rectification in PFC. Current flows back to the input line when the rectified voltage on the filter capacitor is higher than the input instantaneous voltage through the active bridge line rectifier. This causes lower PF and THD values and decreases efficiency at extremely light load, as shown in [Figure 7](#).

Control method for active bridge line rectification

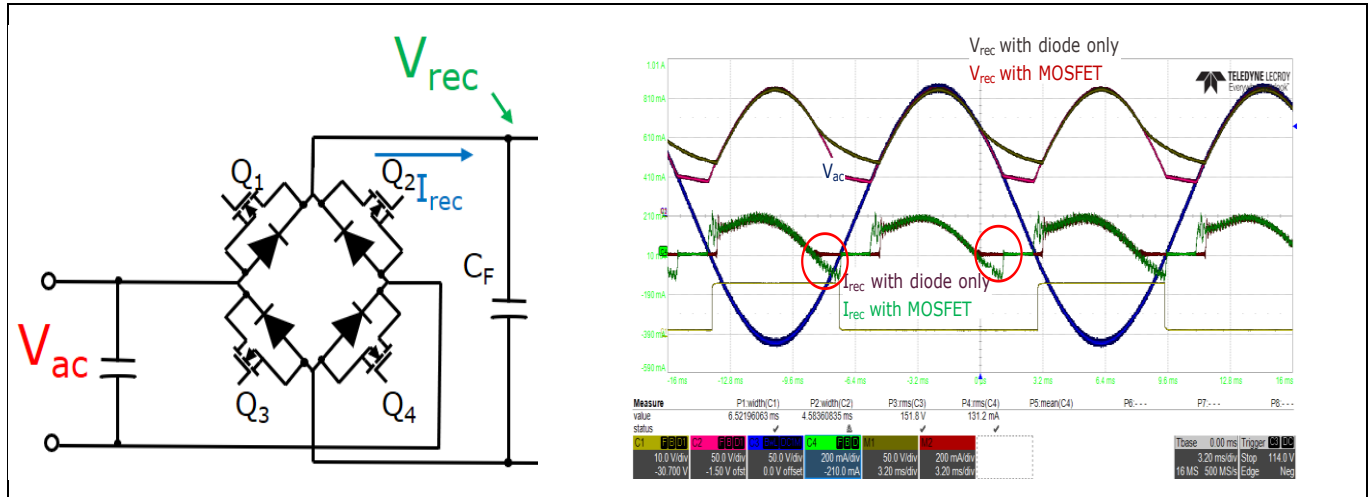


Figure 7 Decreased PF and THD values under light load conditions originating from current flowing back from the filter capacitor to the input line

Two possible solutions are useful for solving such current distortions. First, only use MOSFETs at the low side of active bridge line rectification, like the Q₃ and Q₄ in **Figure 7**. The distortion comes from the discharging current from the filter capacitor to the input line through the MOSFET, as the capacitor voltage is higher than the input instantaneous voltage. MOSFETs provide bi-directional paths for current. Without a MOSFET on the high side, the current never flows from the filter capacitor to the input line. As the efficiency improvement is enough, an active bridge line rectification with a MOSFET only at its low side prevents a worse THD.

Second, using a SR controller as the controller in the active bridge line rectification, shown in **Figure 8**. The control concept behind a SR controller is to detect the voltage level on the MOSFET when it is on. When the absolute voltage level of the MOSFET changes from high to low, a potential reverse current incident on the MOSFET may occur, and then the controller stops driving the signal. The occurrence of deteriorating PF and THD caused by a reverse current is almost impossible with a SR controller.

Control method for active bridge line rectification

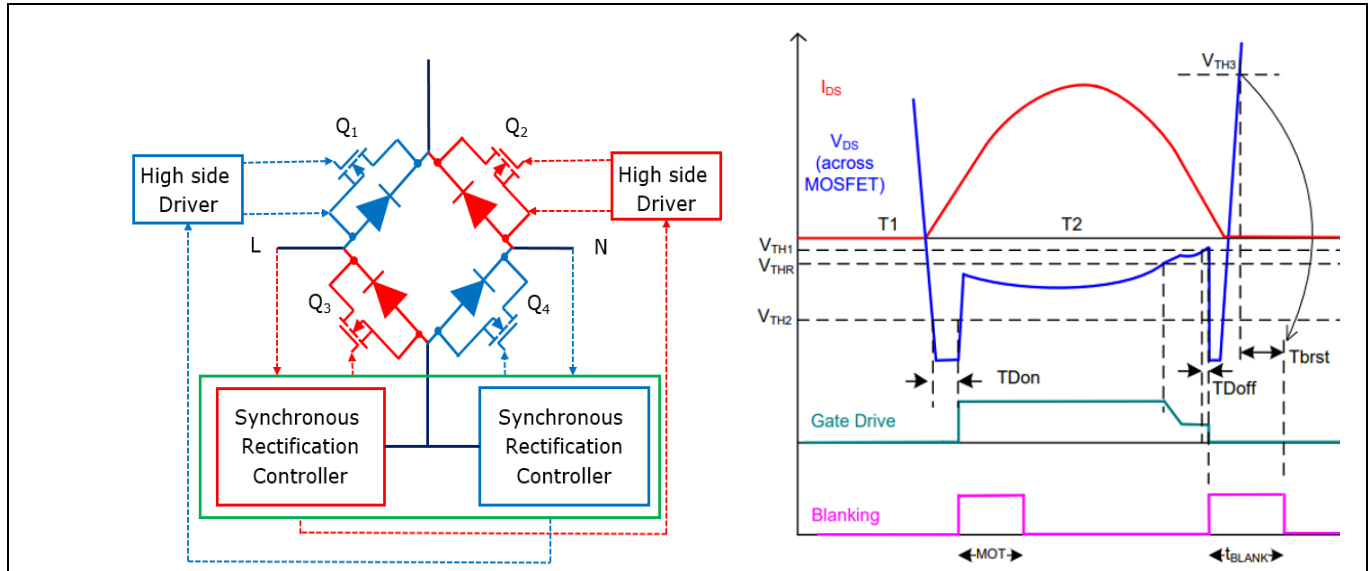


Figure 8 Using a SR controller in active bridge line rectification

It is worth mentioning that deteriorating THD and efficiency at light load caused by an active bridge line rectification depends on the input voltage, filter capacitance and load condition. Faced with these issues, designers may adopt different approaches regarding power supplies for different applications, different PFC topologies and output power. A CCM PFC with low filter capacitance is mostly adopted by power supplies of higher power (kW and above). Under light load testing conditions, such as a 10 percent load, THD and efficiency deteriorations caused by an active bridge rectification might be hardly noticeable. But this is significant in a 200 W adapter with CrM PFC and high filter capacitance, where the aforementioned issues can be noticed under light load conditions. The designers may check the waveform and choose a suitable control method based on the PFC topology, load and test condition.

2.2 Control method of active bridge line rectification for burst mode control

The benefits from active bridge line rectification for power supplies do not only improve efficiency, but also the temperature of the power device, especially for high-density power supplies relying exclusively on natural convection. In external power supplies, like adapters, burst mode control is a necessary function to meet the input power specification at no-load conditions. How does the active bridge line rectification control the MOSFET at burst mode in external power supplies?

Figure 9(a) shows the voltage waveform on a filter capacitor and current through a bridge rectifier without any active bridge line rectification. Few pulse currents are observed, and the input power at no-load conditions meets the specifications. However, the voltage waveform on the filter capacitor and current using active bridge line rectification in **Figure 9(b)** shows a different scenario. Current through active bridge line rectification consists of a higher-level pulse current and a negative current. The input power of the adapter with active bridge line rectification is much higher than that without active bridge line rectification at no-load conditions. The increment is around at 70 mW as provided by a real test. The external power supply with an activated active bridge line rectification does not meet the power specification at no-load conditions.

Control method for active bridge line rectification

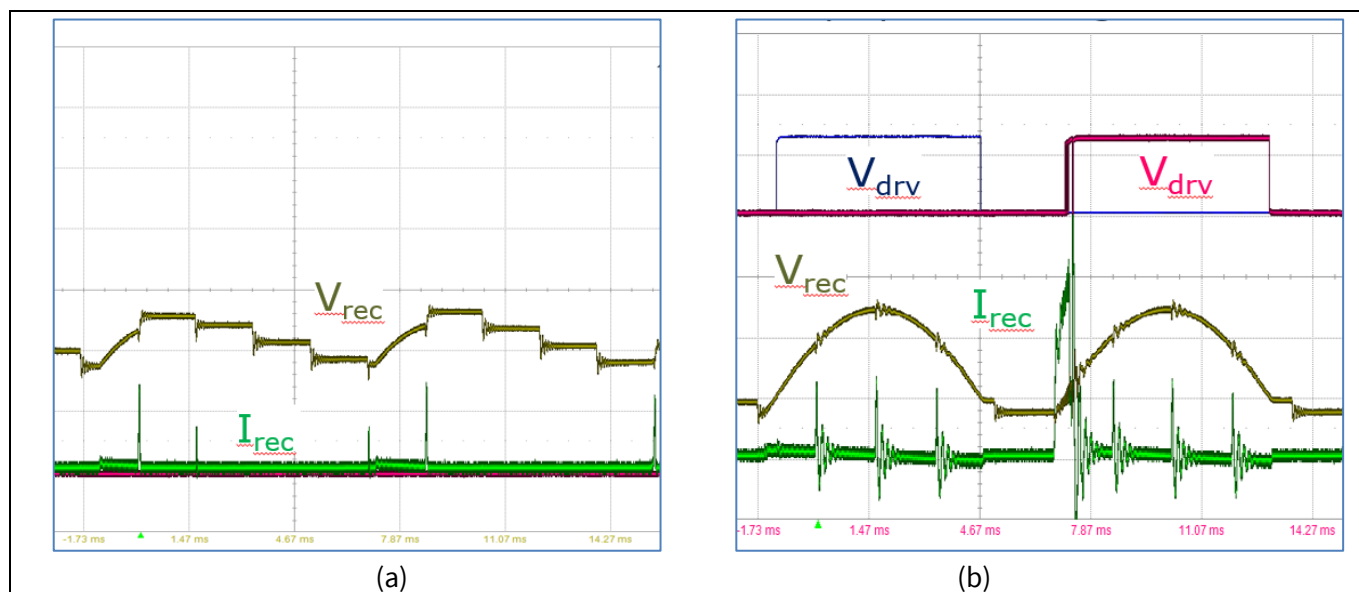


Figure 9 In burst mode, rectified voltage and current waveform (a) without active bridge line rectification; (b) with active bridge line rectification

An activation function for the active bridge line rectification used in external power units with burst mode is necessary through using a V_{CC} power circuit with a burst mode indication signal from the main board, as shown in [Figure 10](#).

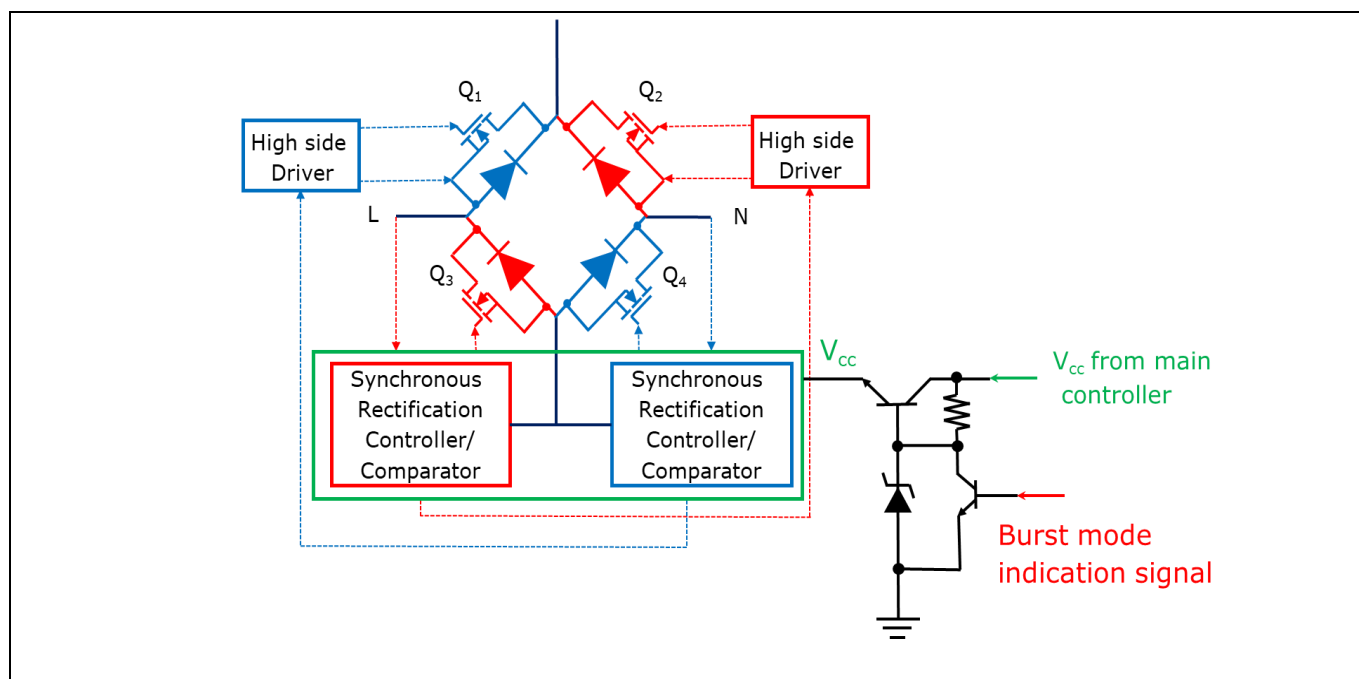


Figure 10 V_{CC} power circuit deactivates active bridge line rectification in burst mode

MOSFET selection for active bridge line rectification

3 MOSFET selection for active bridge line rectification

Switching loss and conduction loss of MOSFET are the losses that lead its temperature increasing. The switching loss of MOSFET in active bridge line rectification can be almost ignored due to the switching frequency of the MOSFET being the line frequency; the conduction loss of MOSFET depends on the current and the MOSFET $R_{DS(on)}$. MOSFET which relies on the die and package technology, is the key factor to achieve high performance in active bridge line rectification.

The challenges for MOSFET manufacturers in such applications are to produce the lowest MOSFET $R_{DS(on)}$ within the same die area and to create high performance packages with low parasitic resistance and high thermal conductivity. From the characteristic, MOSFET $R_{DS(on)}$ is increasing along with junction temperature. Packages with better heat conductivity help to stabilize the device temperature and minimize a further power dissipation from higher $R_{DS(on)}$ caused by an even higher junction temperature.

High power density design is one of the key features for power supply units that utilize active bridge line rectification for both efficiency and thermal considerations. The same $R_{DS(on)}$ of MOSFET in a smaller package or a smaller $R_{DS(on)}$ of MOSFET in the same package is the criteria to select the MOSFET for this application.

Therefore, a comparison of the lowest MOSFETs $R_{DS(on)}$ from different manufacturers in the market is shown in **Figure 11**. The lowest MOSFETs $R_{DS(on)}$ in TO247 package is 10mΩ in the market that is manufactured by Infineon technology. That fact demonstrates the advance silicon technology of power MOSFET in Infineon. Considering the MOSFET in the SMD package, the lowest MOSFET $R_{DS(on)}$ in TOLL package is 22mΩ.

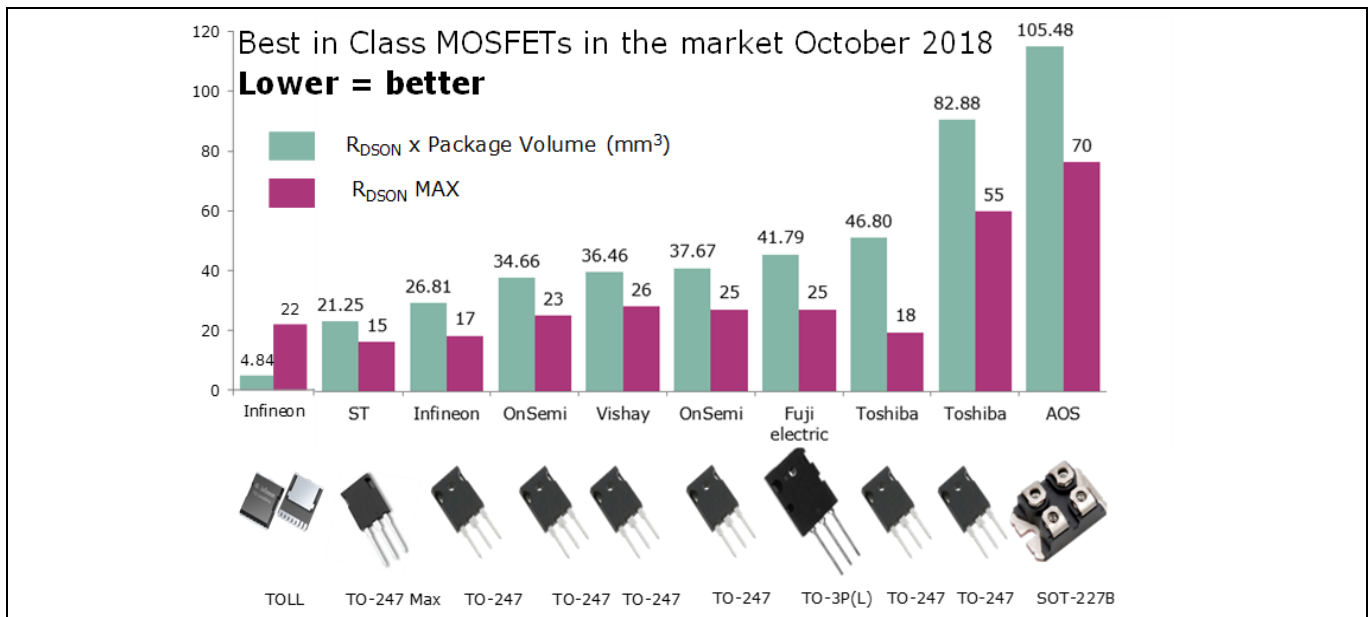


Figure 11 Comparison of lowest $R_{DS(on)}$ of MOSFETs from different manufacturers

Figure 12(a) shows Infineon's lowest $R_{DS(on)}$ in different packages. TO247 is the possible selection if considering the lowest $R_{DS(on)}$ in one package. 10mΩ is the lowest $R_{DS(on)}$ value in this packages. However, when considering the $R_{DS(on)}$ and package area, TOLL is the most suitable package as its lowest $R_{DS(on)}$ is 22mΩ. Accordingly, ThinPAK is another good choice with the smallest package volume and lowest $R_{DS(on)}$ at 60mΩ.

MOSFET selection for active bridge line rectification

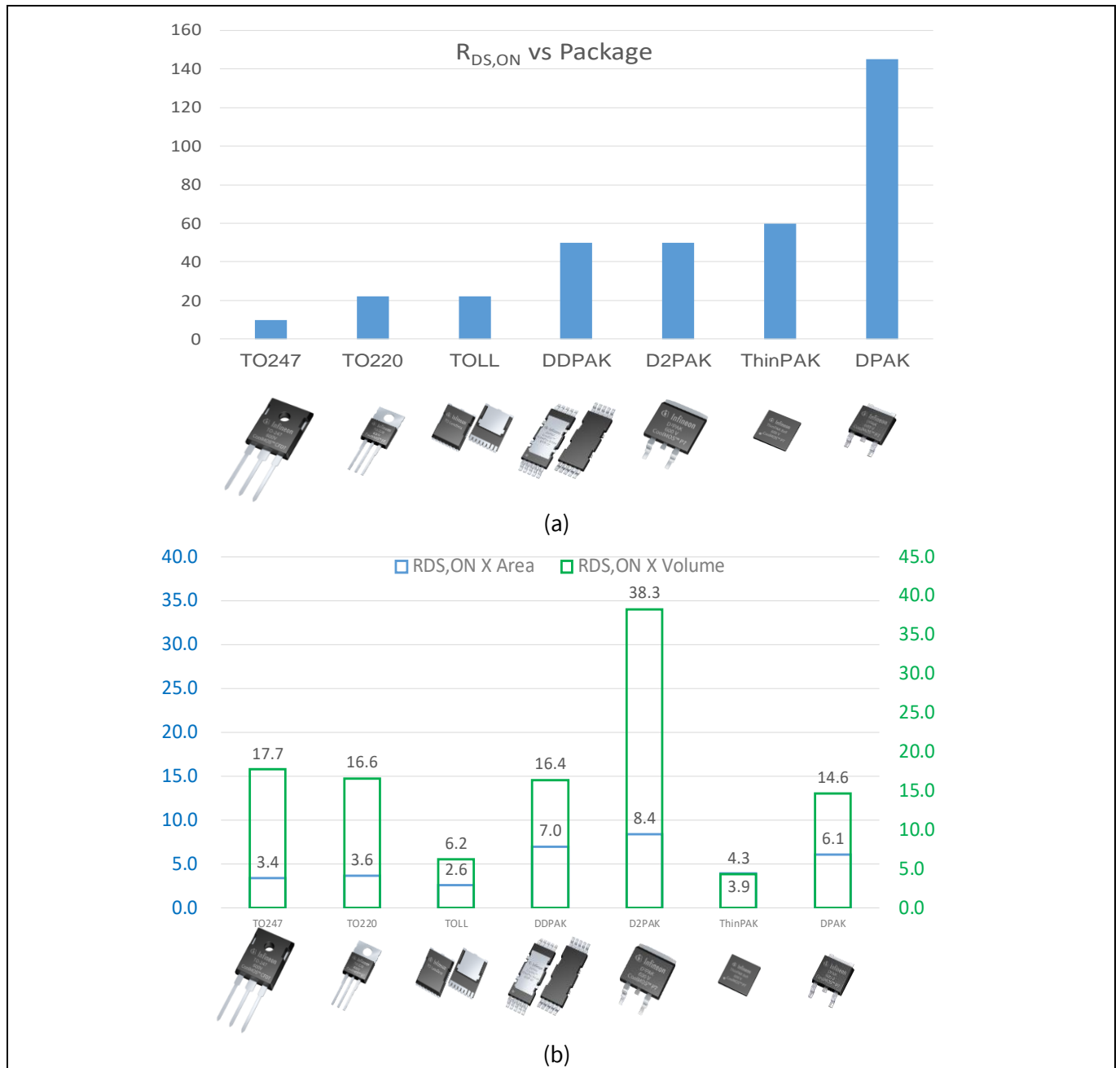


Figure 12 Comparison of Infineon's lowest $R_{DS(on)}$ in different packages (a) by $R_{DS(on)}$ value; (b) by package area and package volume

MOSFET selection for active bridge line rectification

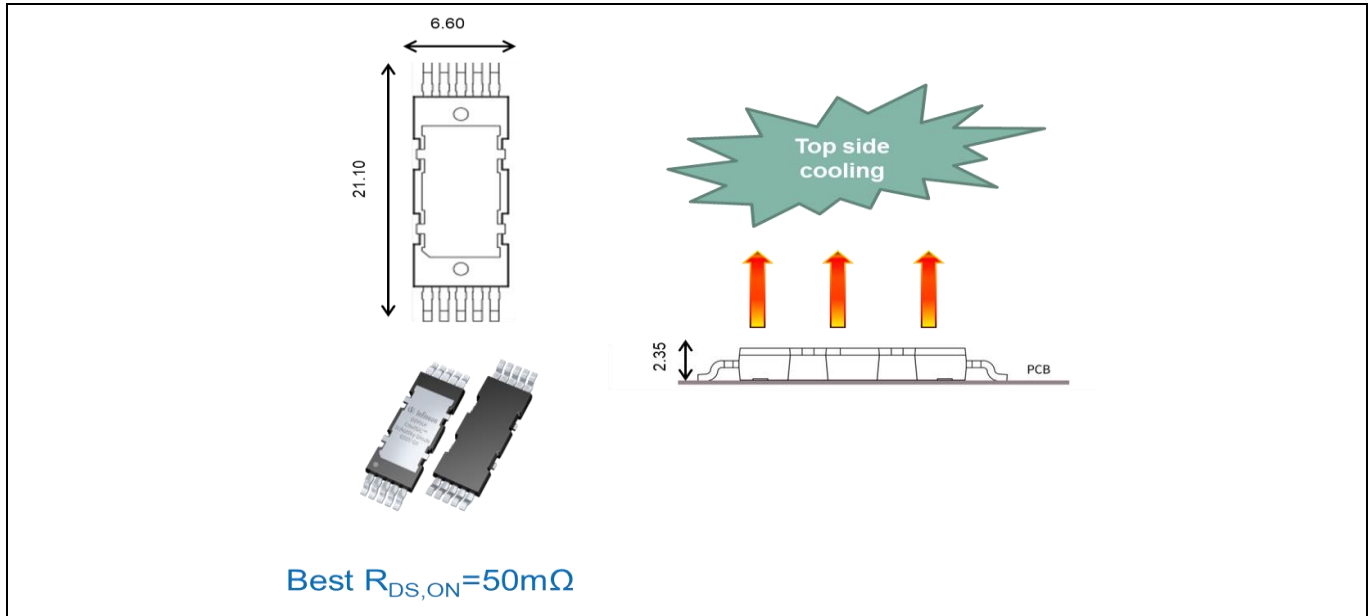


Figure 13 Infineon's top-side cooling SMD packages – DDPAK

A heat sink is helpful for thermal conduction for top-side cooling of the DDPAK as shown in [Figure 13](#). The heat can spread via the lead frame on the top side of the MOSFET to the heat sink and then to the environment. The lowest $R_{DS(on)}$ in DDPAK is 50mΩ.

In addition, height is one of the constraints, especially in high power density power supply units. [Figure 14](#) shows four daughter boards with MOSFETs in different packages designed for height constraints of different power supply units. Considering the space and outline, ThinPAK and DDPAK are suitable for low-profile power supply units. The maximum height of the daughter board with these two packages is 20 mm.

The daughter board shown here is helpful for immediately evaluating the performance of active bridge line rectification with the customer's current power supply. Another possible daughter board design is to divide active bridge line rectification into two parts: upper bridge with driver and lower bridge with controller. The control signals between both boards are connected via the main board. With such daughter board structures, even a TOLL package may be utilized in power units with a height constraint of 20 mm.

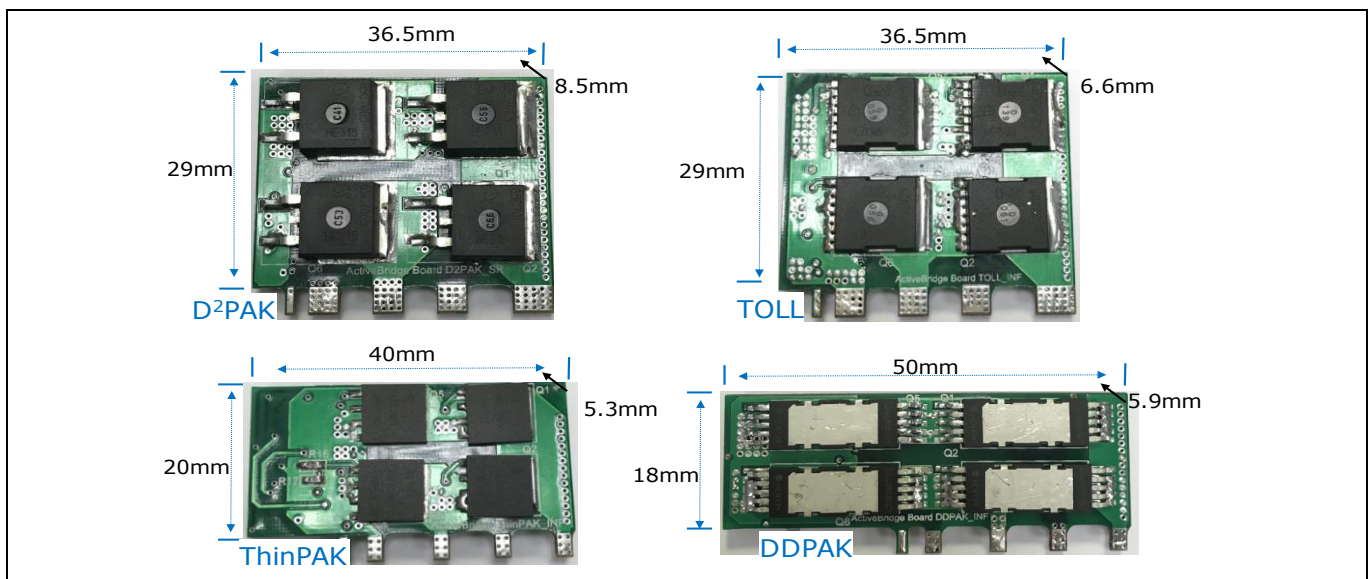


Figure 14 Active bridge line rectification daughter board with MOSFETs of various packages for visual concept

Device replacement and power loss calculation

4 Device replacement and power loss calculation

4.1 Formula for calculating the conduction loss of bridge diodes and MOSFETs

The advantage of active bridge line rectification for power supply is not only to improve the efficiency from light load to full load, but also to improve the temperature of the power device. To estimate the efficiency improvement made by active bridge line rectification, the power dissipation of a bridge rectifier and power MOSFET needs to be calculated first.

The equivalent diode circuit is considered as a DC potential, V_T , in series with an equivalent resistance, R_D , as shown in [Figure 15](#). The formula for conduction loss of the diode is:

$$P_{con} = V_T \times I_{D,avg} + I_{D,rms}^2 \times R_D (@specified T_J)$$

Where $I_{D,avg}$ and $I_{D,rms}$ is the average current and effective current of the diode, respectively.

Moreover, the MOSFET is considered as a resistance, which is the $R_{DS(on)}$ at a specified junction temperature. The conduction loss of the MOSFET can be calculated by:

$$P_{con} = I_{D,rms}^2 \times R_{DS,ON} (@specified T_J)$$

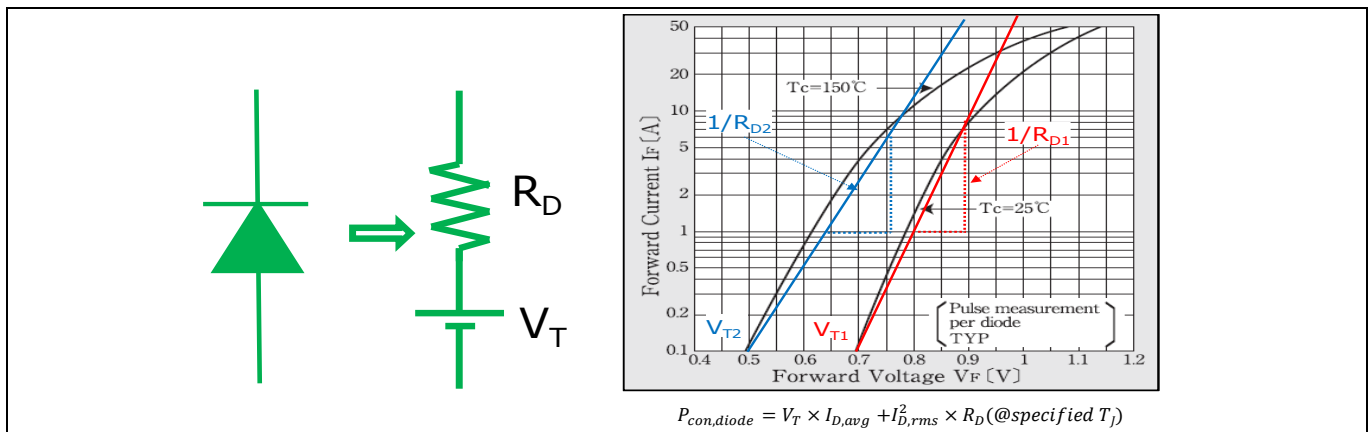


Figure 15 The equivalent circuit and the conduction loss of the diode

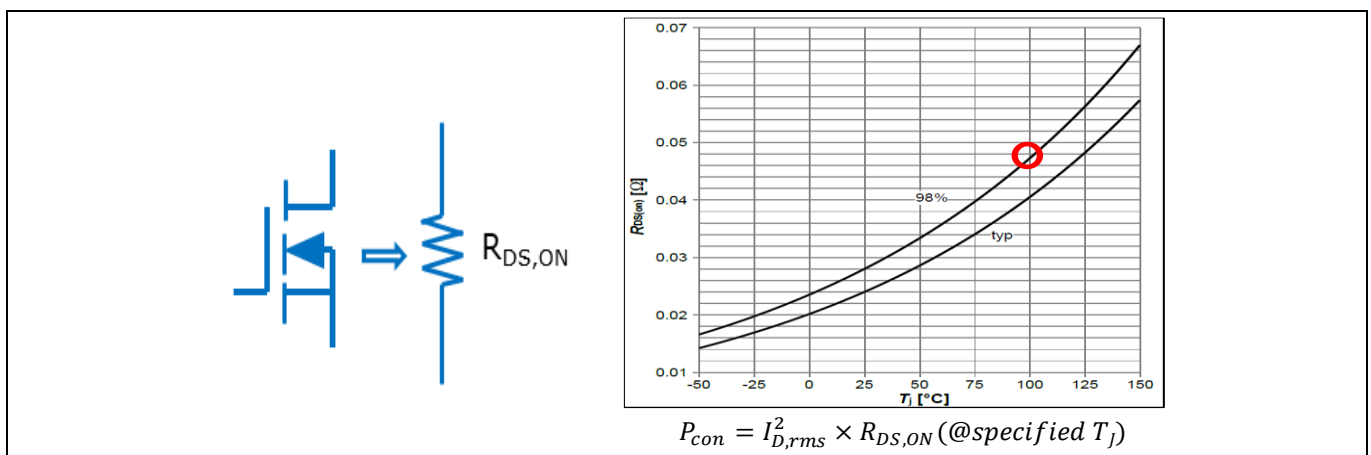


Figure 16 The equivalent circuit and the conduction loss from $R_{DS(on)}$ of the power MOSFET

Device replacement and power loss calculation

Theoretically, it is simple to calculate the power loss improvement by subtracting the power dissipation of the MOSFET from that of the bridge rectifier. The efficiency improvement can be obtained from the power loss reduction at different load conditions. However, it is not simple in real calculations for the following reasons:

- The equivalent circuit of diode power dissipation is considered as DC potential in series with an equivalent resistance. However, these two parameters are not fixed and change along with the temperature and current of the diode. The curves at all of the possible temperatures are not provided by the manufacturers. In most cases, only curves at 25°C and 150°C are found in the datasheet.
- The $R_{DS(on)}$ of the MOSFET varies along with its junction temperature and current. However, the PCB parasitic resistance is not ignored when using an extremely low $R_{DS(on)}$ device, such as 10 mΩ, which makes it difficult to estimate the power dissipation on active bridge line rectification.

4.2 Estimating the conduction loss of bridge diodes and MOSFETs in real test

It is a challenge to estimate the efficiency improvement at specified load conditions from the diode and power MOSFET conduction loss. A simple circuit as shown in **Figure 17** is used to test and estimate the power dissipation of a bridge diode and power MOSFET. The test is implemented by utilizing a standard resistor as load and adjustable AC voltage source to control the input voltage and load current through a bridge rectifier or MOSFETs.

Measuring the input voltage, output voltage and load current of the test circuit is required for power loss calculation. Measuring the temperature of the bridge rectifier and MOSFET is required for evaluating power dissipation according to the formula. In principle, the load current multiplies the difference between input and output voltage, which is the power dissipation of the bridge rectifier or MOSFET. We may calculate an effective voltage representing the loss of the bridge rectifier and MOSFET.

This measurement result is used to verify the accuracy of power loss calculation based on the formula.

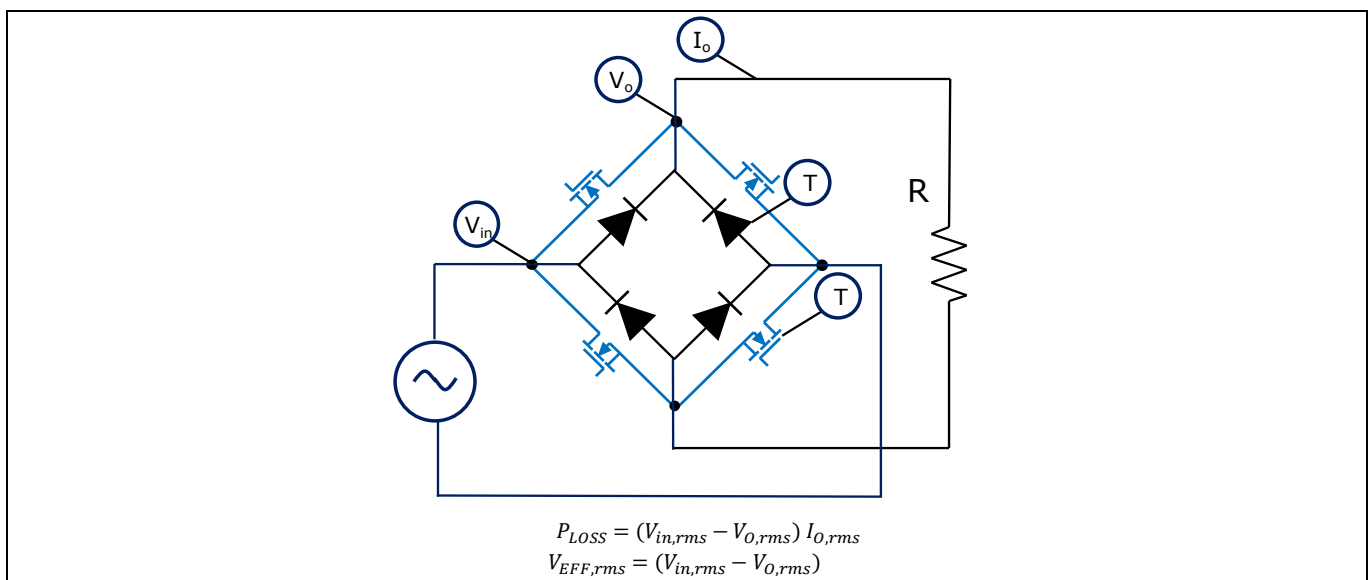


Figure 17 Power dissipation test circuit for the bridge rectifier and active bridge line rectification

The first test is implemented with a bridge rectifier, GBJ1506, under natural convection only. Device temperature is recorded as well, as shown in **Figure 18(a)**. The effective voltage and power loss under various load currents is calculated in **Figure 18**.

Device replacement and power loss calculation

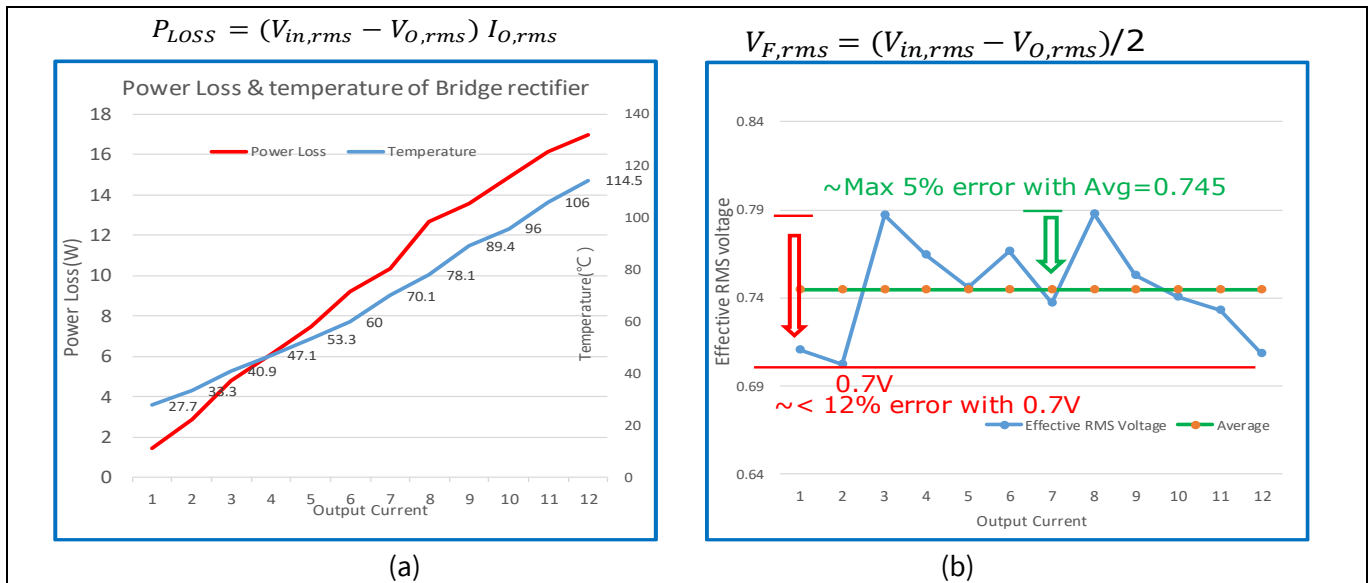


Figure 18 (a) Temperature and calculated power loss for the bridge rectifier, GBJ1506; (b) effective voltage of a bridge rectifier along with load current

Figure 18(a) shows that temperature and power dissipation of the bridge rectifier increasing according to load current. The difficulty of estimating the power loss or effective forward voltage of a bridge rectifier at specified loads is that a higher device temperature leads to a lower forward voltage, but a higher current leads to higher forward voltage. The blue line in **Figure 19(b)** shows the effective forward voltage distribution at different loads. The average effective forward voltage 0.745 V is obtained as shown by the green line in **Figure 19(b)**. The maximum 5 percent calculation error is obtained by the average forward voltage. However, by using the common 0.7 V forward voltage, the maximum error between calculation and measurement result is around 12 percent.

The test can be repeated with fan cooling. **Figure 19** shows the average effective voltage of a bridge rectifier. The effective forward voltage is close to the 0.784 V average value only under 1 A conditions, where the maximum error is 7 percent. The maximum error is 13 percent calculated with the 0.7 V forward voltage.

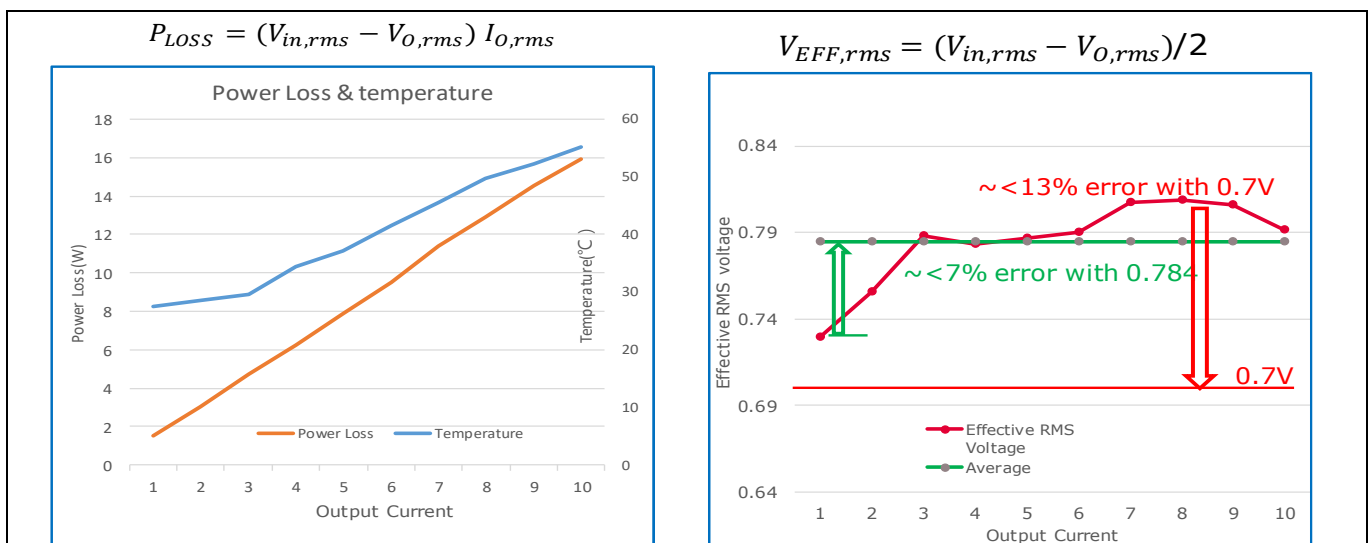


Figure 19 Power loss, temperature and effective forward voltage of a bridge rectifier with fan cooling

Device replacement and power loss calculation

The full-wave active bridge line rectification test at 22 mΩ was repeated with natural convection and fan cooling; test results are shown in **Figure 20** and **Figure 21**. The power dissipation is quite low due to the small MOSFET $R_{DS(on)}$. However, the error between calculation and measurement is not small, with the highest being around 30 percent.

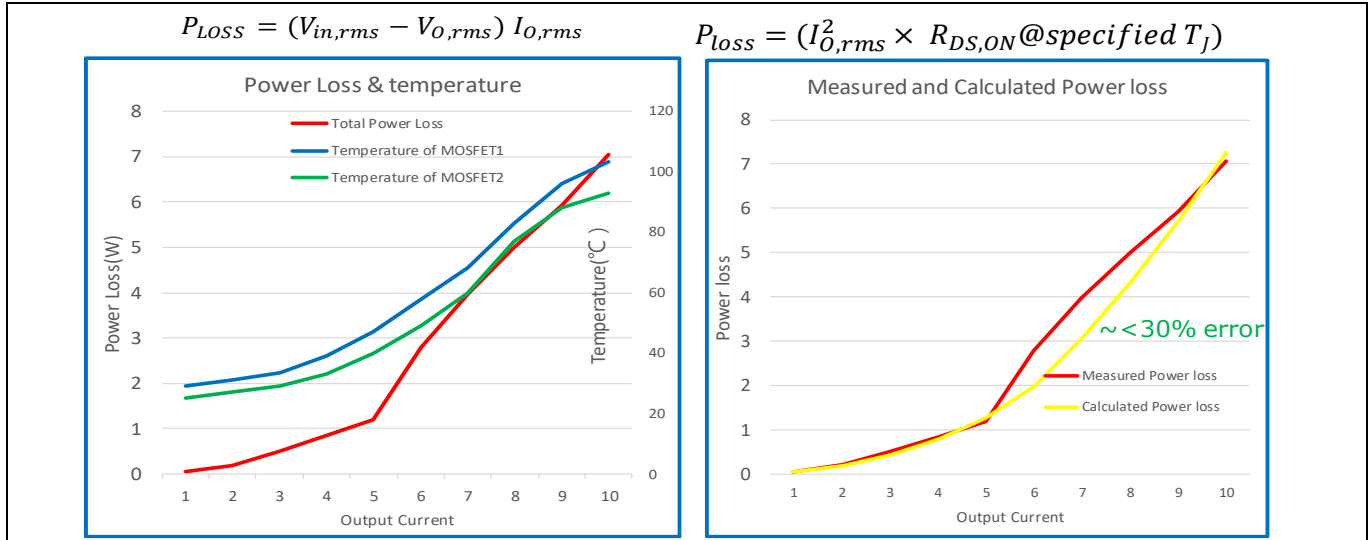


Figure 20 Device temperature and power dissipation of active bridge line rectification at 22 mΩ under natural convection and different loads

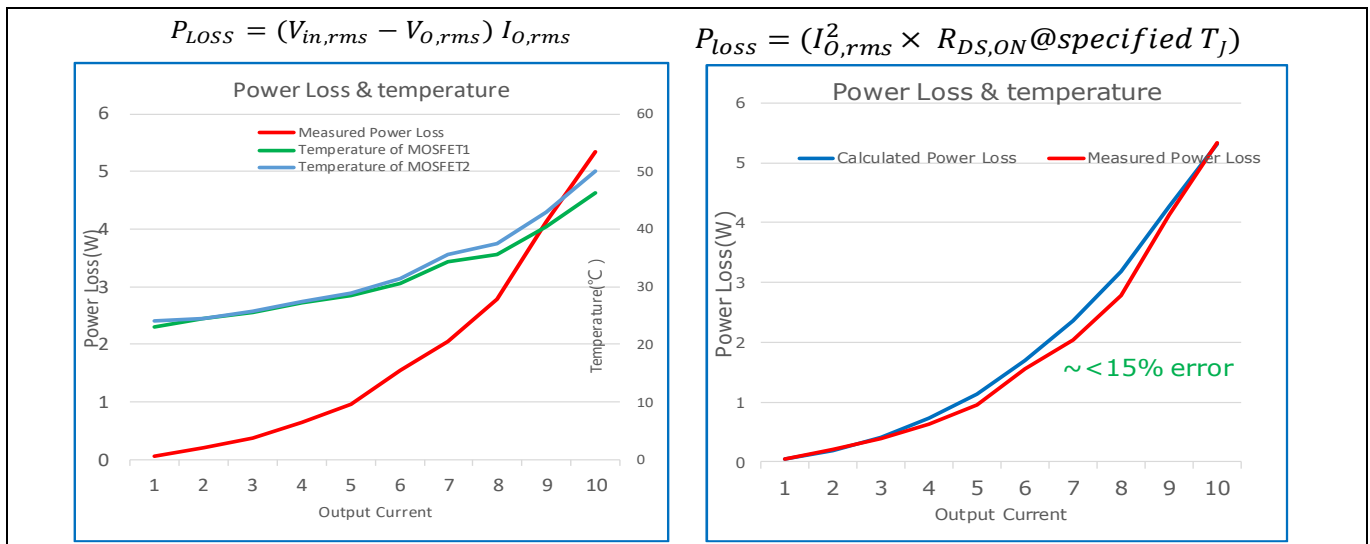


Figure 21 Device temperature and power dissipation of active bridge line rectification with 22 mΩ under fan cooling and different loads

For some applications that need slight efficiency improvements, half-wave of active bridge line rectification is good enough. This is accomplished with two MOSFETs on the low side of the active bridge line rectification.

Device replacement and power loss calculation

The test was repeated with two MOSFETs, and the results are shown in **Figure 22** and **Figure 23**. **Figure 22** shows the test results under natural convection, and the error between measurement and calculation of power dissipation is only 5 percent by utilizing the formula $V_{EFF,rms}=0.7+I_{O,rms}\times R_{DS(on)}@specified\ T_J$ for calculating the effective forward voltage in combination with a bridge rectifier and half-wave active bridge line rectification; with fan cooling, the error between measurement and calculation of power dissipation is only 7 percent by utilizing the formula of $V_{EFF,rms}=0.75+I_{O,rms}\times R_{DS(on)}@specified\ T_J$.

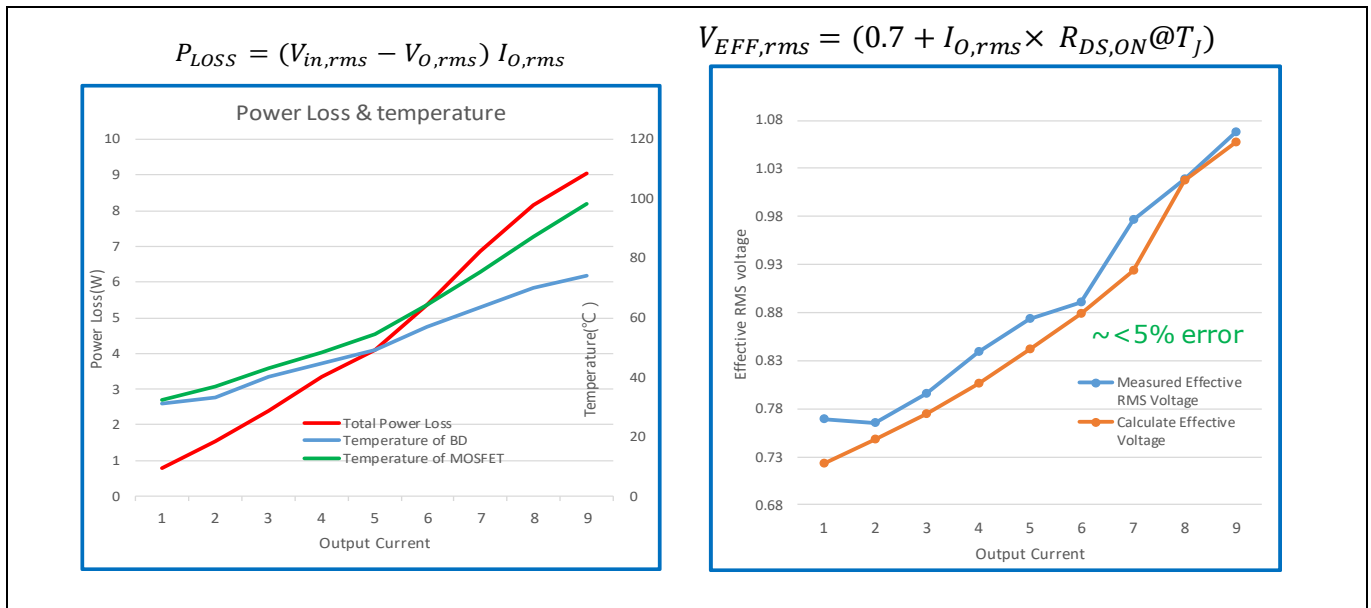


Figure 22 Effective forward voltage, power loss and device temperature of bridge rectifier and half-wave active bridge line rectification under natural convection

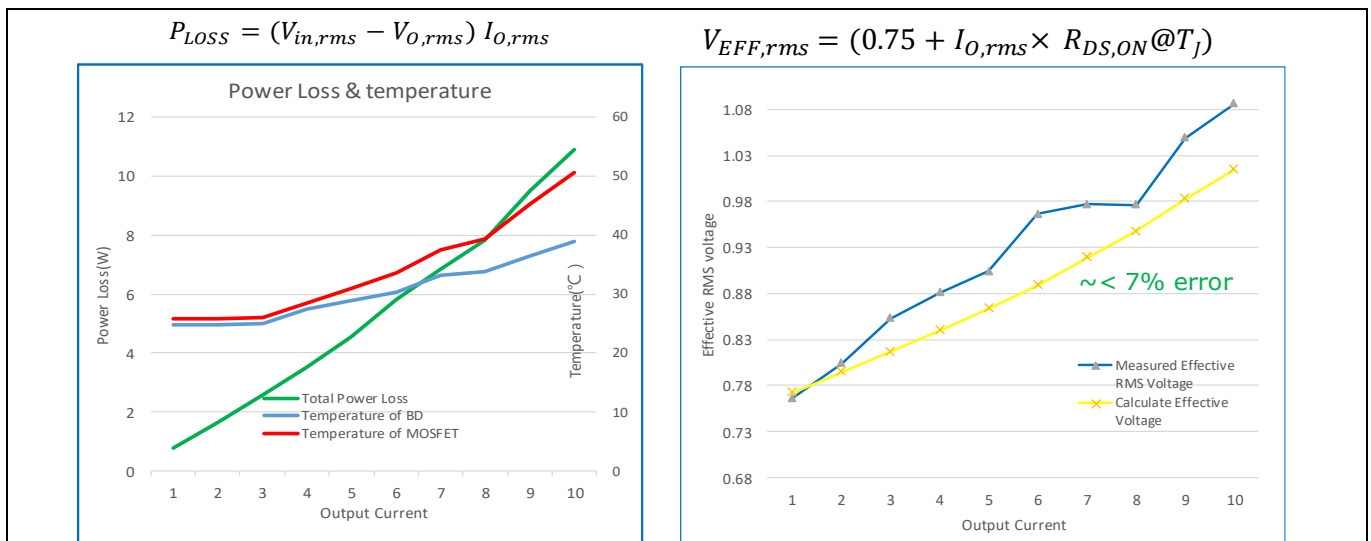


Figure 23 Effective forward voltage, power loss and device temperature of bridge rectifier and half-wave active bridge line rectification under fan cooling

Device replacement and power loss calculation

As indicated by the test results, the effective forward voltage of a bridge rectifier with fan cooling is a little bit higher than that with natural convection due to lower device temperature.

Based on the above results, errors between calculation and measurement always exist, considering the power dissipation of the bridge rectifier and MOSFET only. In fact, these devices' calculations are conducted in order to estimate the efficiency improvement at specified load conditions. Even though an error exists considering the power dissipation of the device, we only need to focus on the efficiency improvement of the power supply, not on the devices themselves. The power loss reduction should turn into efficiency improvement at input current of 115 V AC and 230 V AC respectively, as shown in **Figure 24** and **Figure 25**.

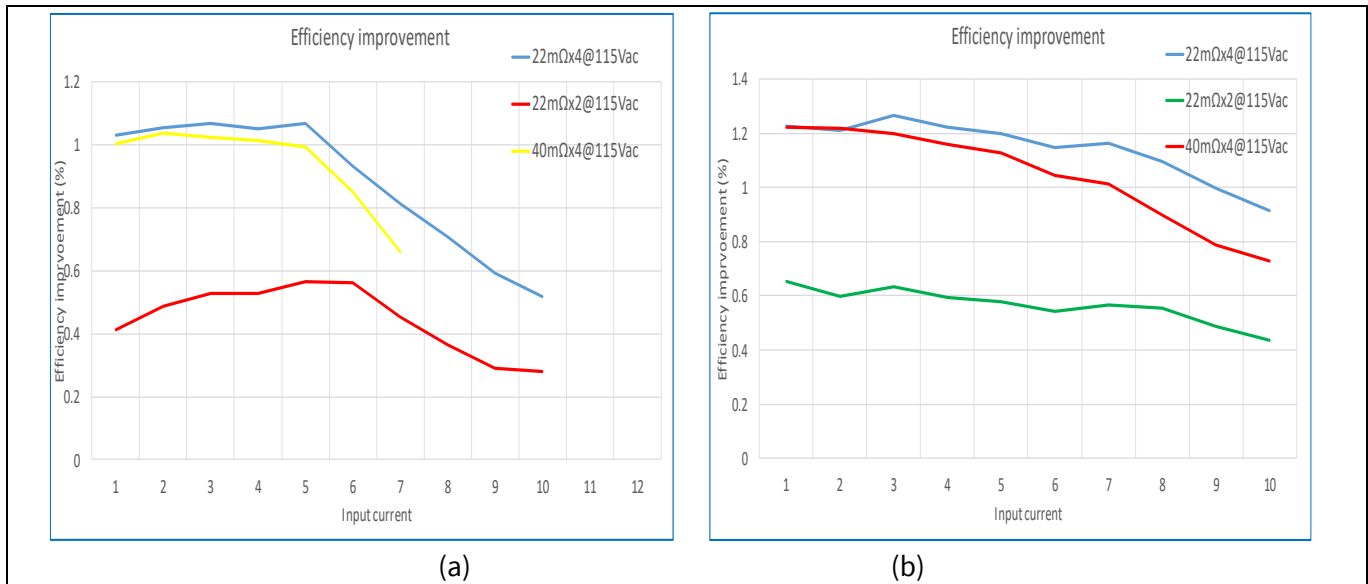


Figure 24 Efficiency improvement at different loads of full-wave with 22 mΩ/44 mΩ and half-wave with 22 mΩ of active bridge line rectification at $V_{in} = 115$ V AC under (a) natural convection (b) fan cooling

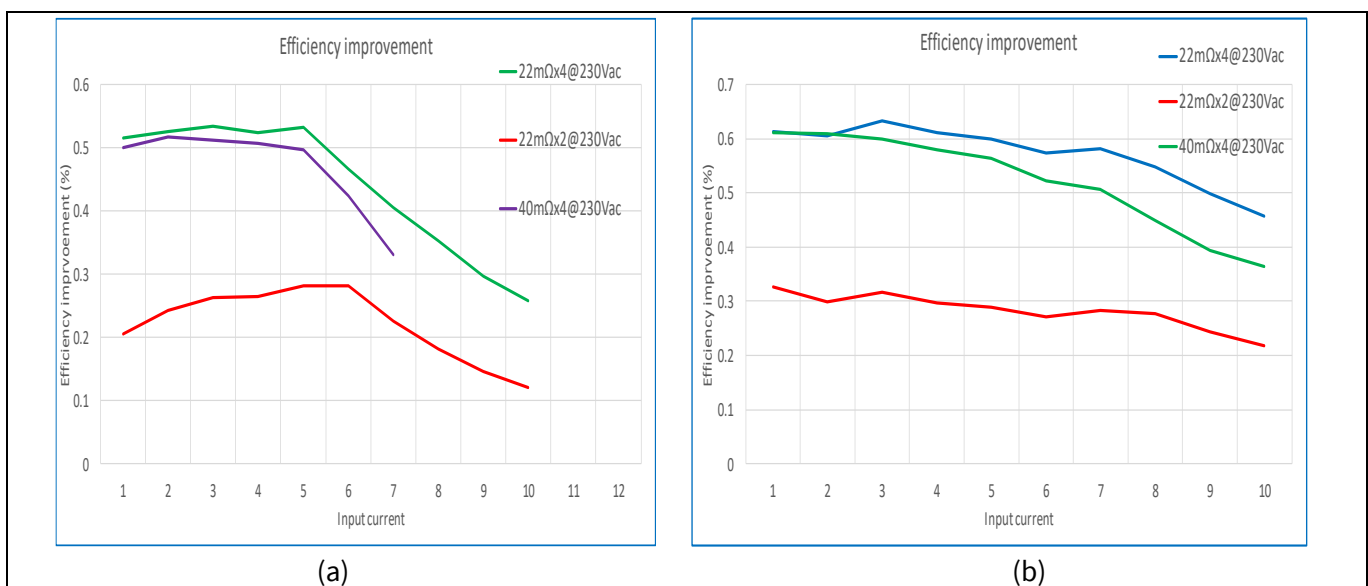


Figure 25 Efficiency improvement at different loads of full-wave with 22 mΩ/44 mΩ and half-wave with 22 mΩ of active bridge line rectification at $V_{in} = 230$ V AC under (a) natural convection (b) fan cooling

Device replacement and power loss calculation

According to the test results in this section, designers can choose full-wave or half-wave active bridge line rectification with different $R_{DS(on)}$. In general, full-wave active bridge line rectification with low $R_{DS(on)}$ improves the efficiency the most; half-wave active bridge line rectification with low $R_{DS(on)}$ improves efficiency slightly.

It is a rule of thumb that the $R_{DS(on)}$ of a MOSFET in this application should be less than 100 m Ω due to thermal considerations and especially with natural convection.

Surge voltage and surge current solutions for active bridge line rectification

5 Surge voltage and surge current solutions for active bridge line rectification

5.1 Solutions for surge voltage in active bridge line rectification

A lightning surge voltage test, such as the IEC-61000-4-5, is a basic test for all of SMPS units. **Figure 26** shows the lightning test circuit, in which high voltage is generated by a combination wave generator and transferred via a resistor and decoupling capacitor to the power unit.

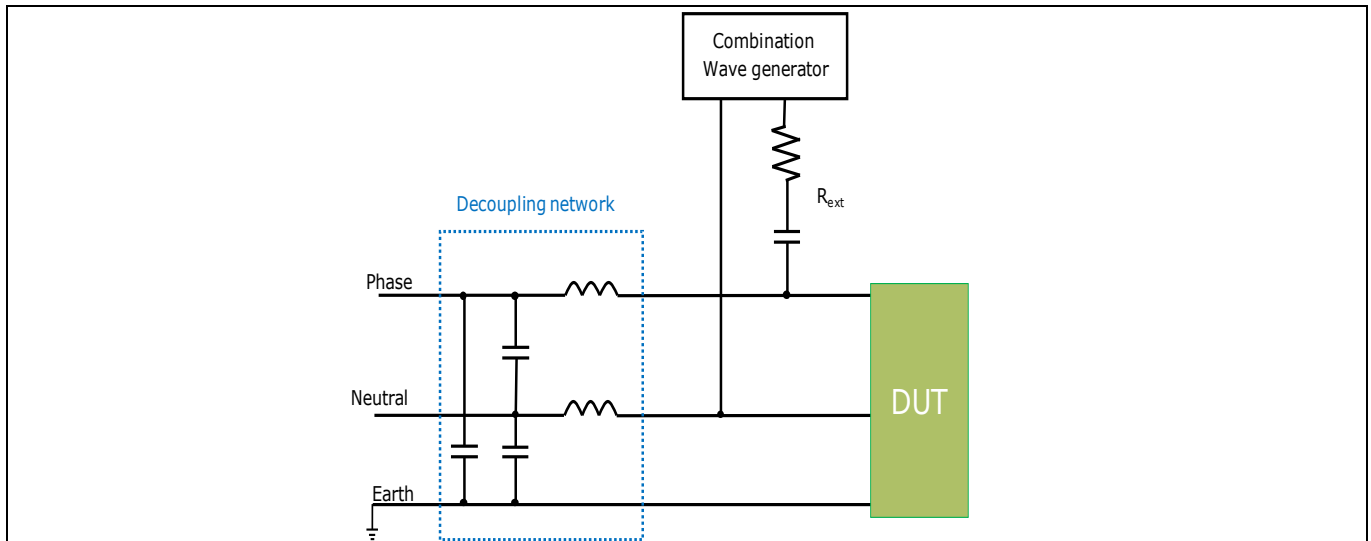


Figure 26 IEC-61000-4-5 test circuit

The IEC-61000-4-5 standard defines the voltage waveform in open-circuit mode, and current waveform in short-circuit mode, as shown in **Figure 27**. Applications and products should comply with the corresponding standard class. In general, the adapter should comply with class 2 standards; class 3 standards apply to server applications.

The surge current capacity of a bridge rectifier is much higher compared to a power MOSFET. For instance, the bridge rectifier has a current capacity of 350 A within 10 ms. Besides current capacity, the maximum reverse voltage of a bridge rectifier that you can find in the market is 1000 V. This means high voltage and current specifications of a bridge rectifier are the possible solutions in case of damage caused during an abnormal test. However, within the application circuit, active bridge line rectification is parallel to the bridge rectifier. It is imperative that the surge voltage and current capacity of the MOSFET are considered during abnormal tests.

As the voltage of a MOSFET exceeds its breakdown voltage, the MOSFET may enter avalanche mode. The MOSFET must be able to withstand the surge energy from overvoltage during an abnormal test. For instance, by adopting the IPT60R028G7 in active bridge line rectification, the breakdown voltage is 650 V at $T_{J,max}$, and single-pulse avalanche energy is 288 mJ. Clearly, the surge energy should be absorbed by the protection device or transferred to storage devices; otherwise, the active bridge line rectification MOSFET will be damaged even with a 1 kV lightning surge differential mode. We may rely on surge energy absorbing devices, like the MOV or gas tube; and energy storage devices, like a bulk capacitor. The bypass diode connection within the PFC circuit determines the energy transfer path to the bulk capacitor during a lightning surge test.

Two types of bypass diode connections within a critical-mode PFC circuit with π -type filter are shown in **Figure 28**. **Figure 28(a)** shows a bypass diode connected between the π -type filter and the bulk capacitor; **Figure 28(b)** shows a bypass diode connected between the active bridge line rectifier and the bulk capacitor.

Surge voltage and surge current solutions for active bridge line rectification

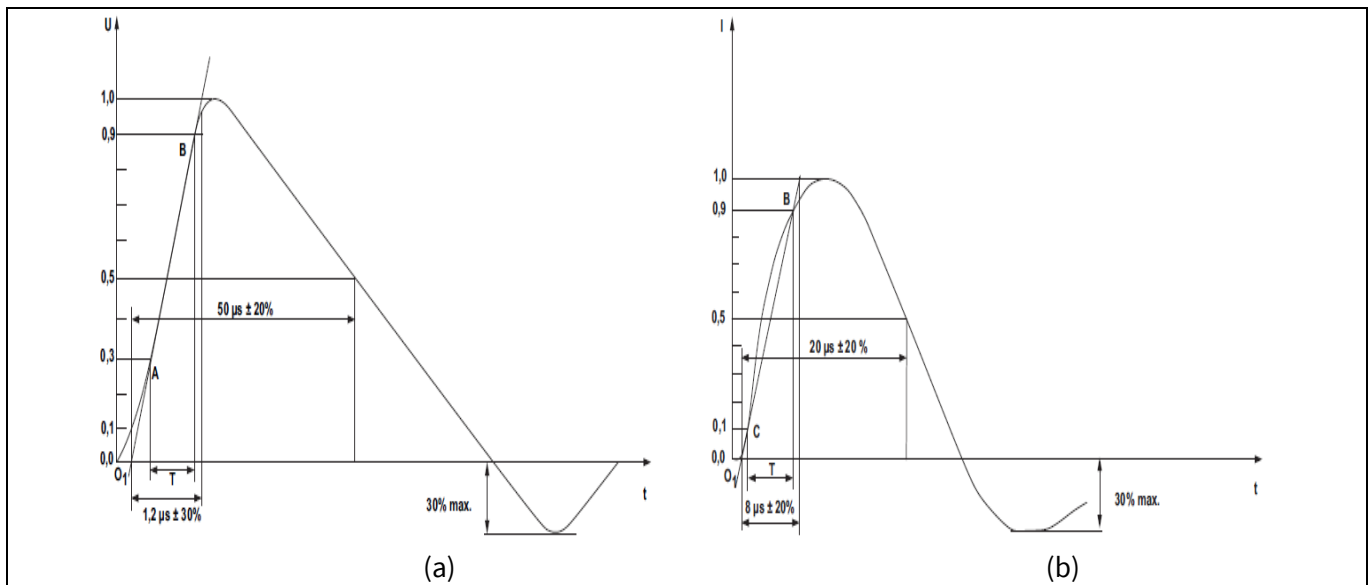


Figure 27 IEC-61000-4-5 standard (a) voltage curve in open circuit mode; (b) current curve in short-circuit mode

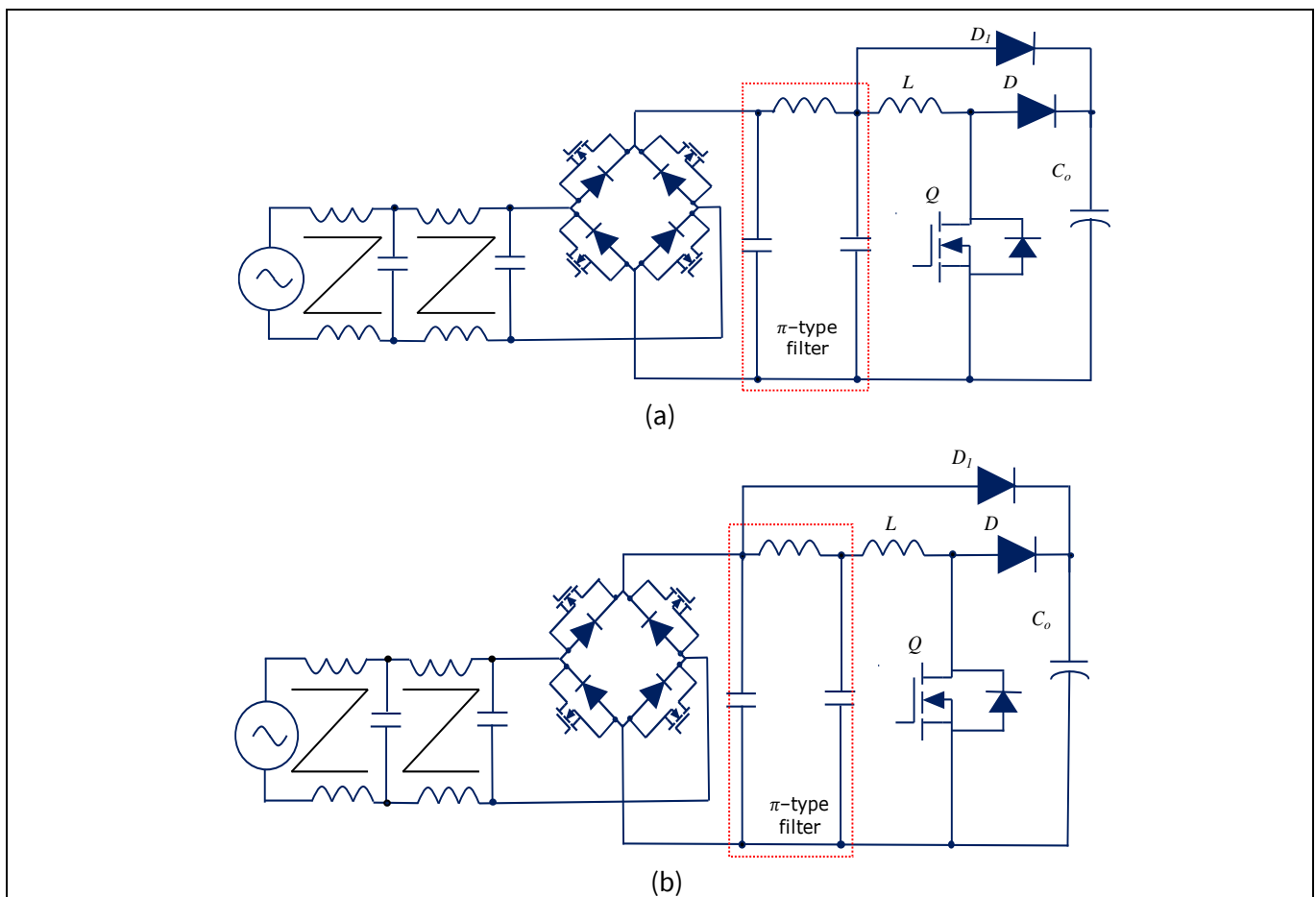


Figure 28 Different energy surge transfer paths in different bypass diode connections

For PFC operations, there is no difference between the two connections in [Figure 28](#). However, with the connection in [Figure 28\(b\)](#), the lightning surge energy can be transferred to the bulk capacitor directly. The MOSFET voltage of the active bridge line rectification will not exceed breakdown voltage. In contrast, the

Surge voltage and surge current solutions for active bridge line rectification

connection in **Figure 28(a)** will have the active bridge line rectification MOSFET damaged due to the lightning surge energy being blocked by the π -type filter in a short time due to surge energy being unable to be transferred to the bulk capacitor directly.

Furthermore, common choke and differential choke are always used at the input terminal for EMI suppression. All of the differential choke or differential inductance from common choke resonate with the capacitor connected to them. A gas tube should be connected with a differential choke or common choke to clamp the resonance voltage winding, as shown in **Figure 29**. MOV is another surge-energy-absorbing device connected to the input terminal. It is worth mentioning that the clamping voltage of the MOV is determined by its leakage current, as shown in **Figure 30**. The leakage current depends on loop resistance and surge voltage value. For higher surge voltage specifications, more part counts of MOV will be necessary to absorb more energy.

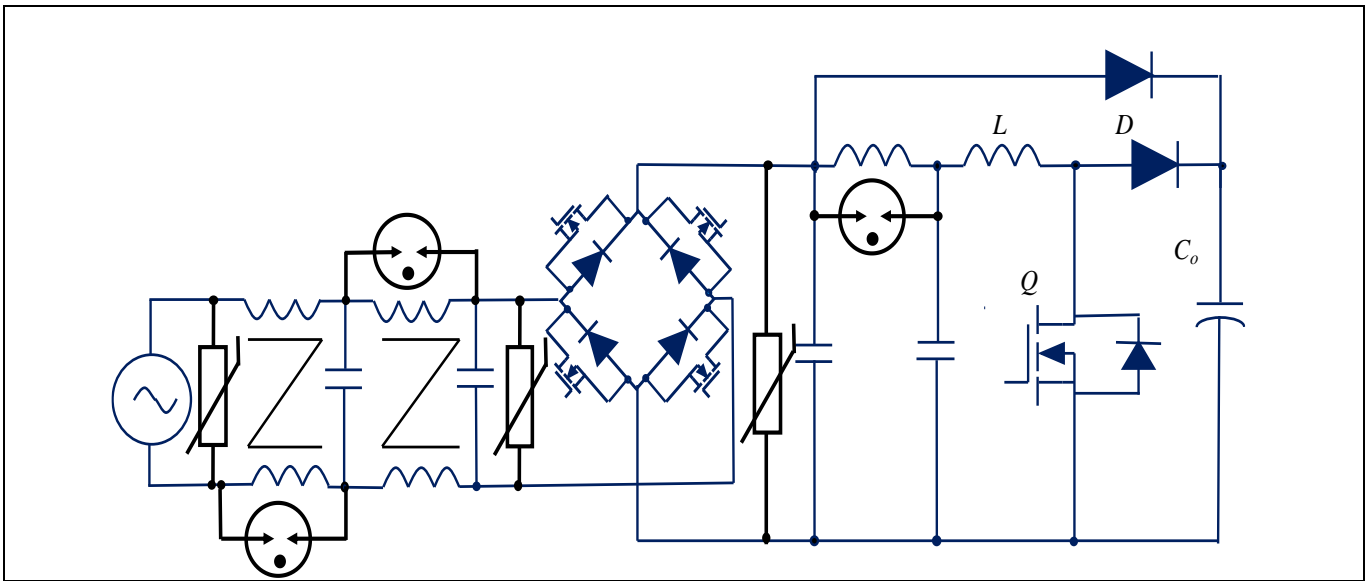


Figure 29 Surge voltage solution for active bridge line rectification

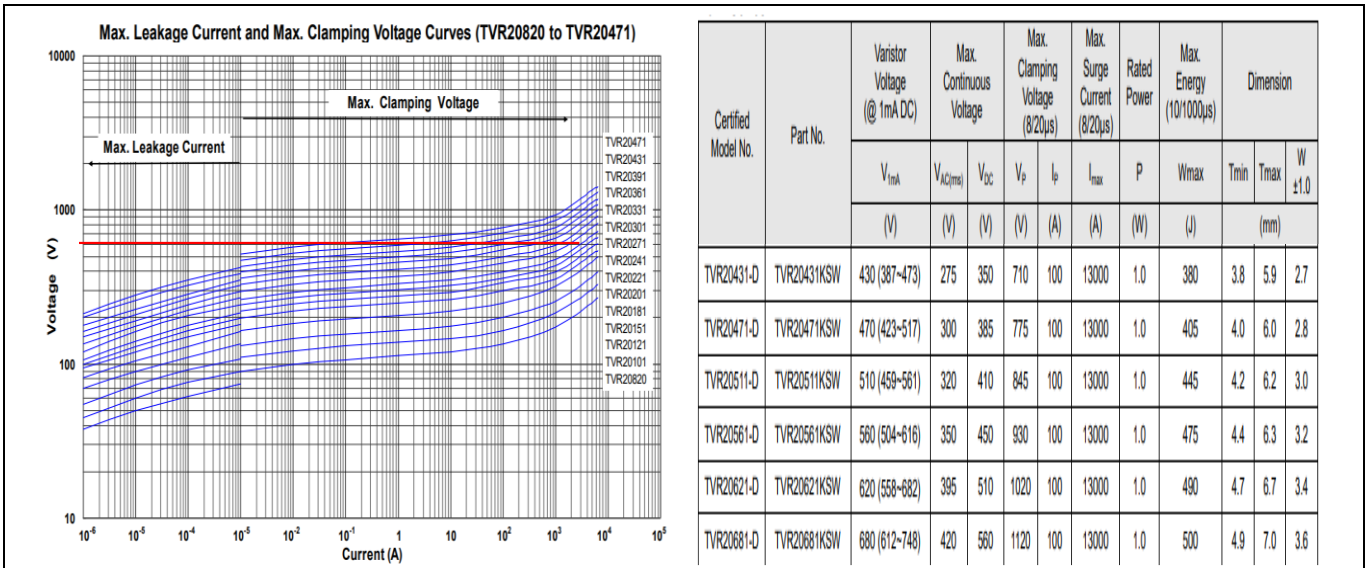


Figure 30 Feature of voltage clamping device, MOV

Surge voltage and surge current solutions for active bridge line rectification

5.2 Solutions for surge current in active bridge line rectification

Some customers raise questions regarding whether the original bridge rectifier is necessary when adopting active bridge line rectification. In terms of current capability, a bridge rectifier is determined by I^2t , but the MOSFET is determined by junction temperature and thermal conduction. From [Figure 31](#) we find that the current capacity of a bridge rectifier is higher than that of a MOSFET when considering time spans longer than 10 ms.

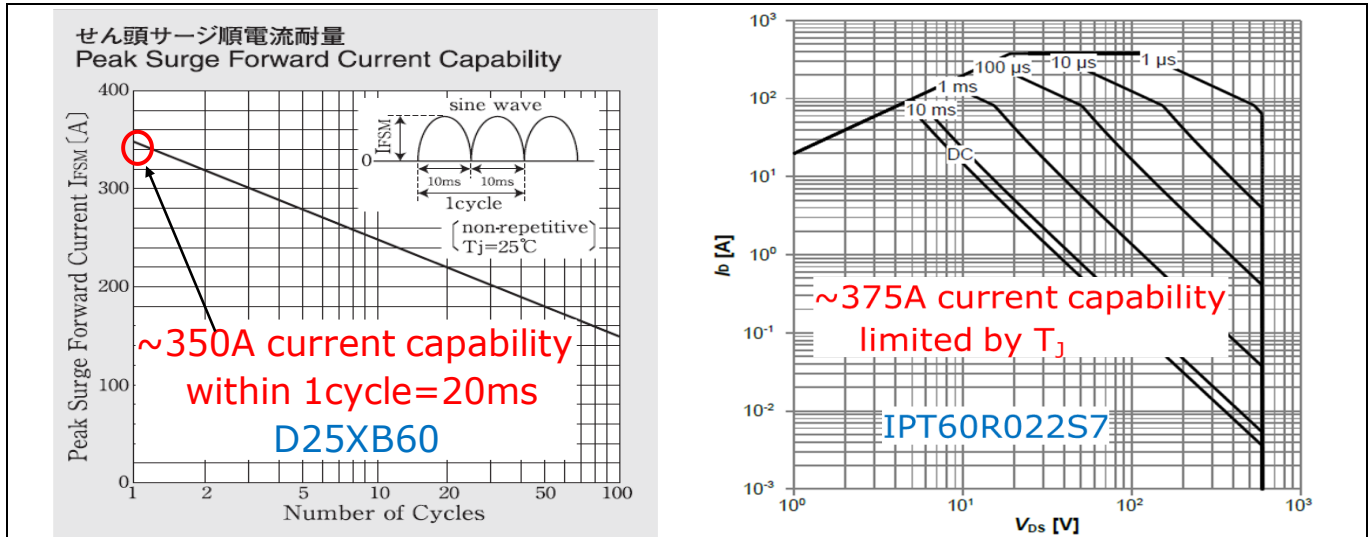


Figure 31 Current capability of a bridge rectifier and MOSFET

Regardless of whether a bridge rectifier or active bridge line rectification is adopted, higher current capacity is required under several conditions:

- (a) Inrush current from the input voltage to charge the bulk capacitor at power up
- (b) Recharging current to bulk capacitor after AC cycle drop-out
- (c) Surge current from a lightning surge voltage test, such as the IEC61000-4-5

The inrush current limitation resistor only suppresses the inrush current at power up. In the other two cases, the active bridge line rectification MOSFETs with lower current capability, compared to a bridge rectifier, cannot easily withstand the surge current, especially during lightning surge voltage test. The surge current may go up to several hundred amperes depending on the surge voltage level and loop resistance.

Assuming the bridge rectifier and active bridge line rectification are parallel, prior to power up, the driving voltage of the active bridge line rectification has not been established. Without the driving voltage, the bridge rectifier and MOSFET are parallel, acting as two diodes. From the forward voltage of the MOSFET and bridge rectifier, the MOSFETs' body diodes conduct the majority of total current due to lower forward voltage. As the temperature of the MOSFETs increases, the MOSFETs' body diodes conduct more current; the current sharing then becomes more unbalanced due to the negative temperature coefficient. [Figure 32](#) shows a higher current through the body diode of the MOSFET as the MOSFET temperature is increasing.

Surge voltage and surge current solutions for active bridge line rectification

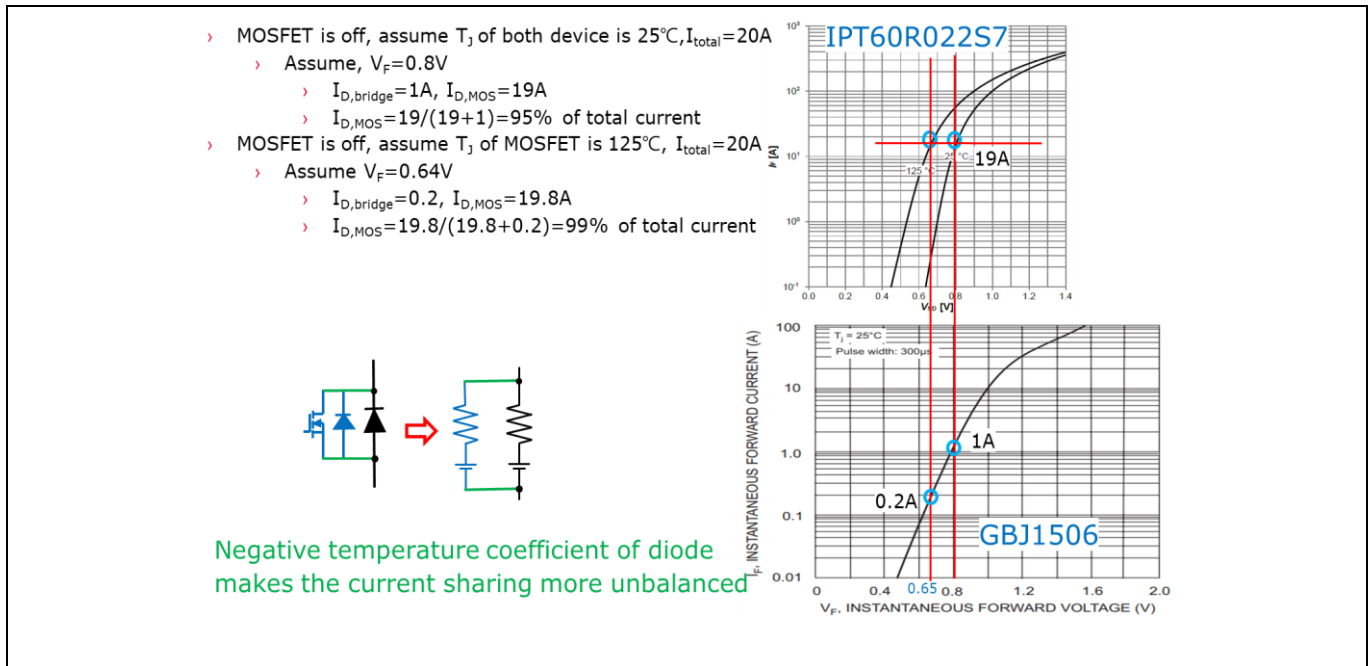


Figure 32 Current sharing between a bridge rectifier and the body diode of a MOSFET

With driving voltage, the active bridge line rectification MOSFET conducts the majority of the total current as the product of the current, and $R_{DS(on)}$ is lower than the forward voltage of the bridge rectifier, as shown in **Figure 33**. MOSFETs with driving voltage represent a power device of positive temperature coefficient; when in parallel with a bridge rectifier, better current sharing is attained even when the temperature of the device has increased, as illustrated in **Figure 34**.

Surge voltage and surge current solutions for active bridge line rectification

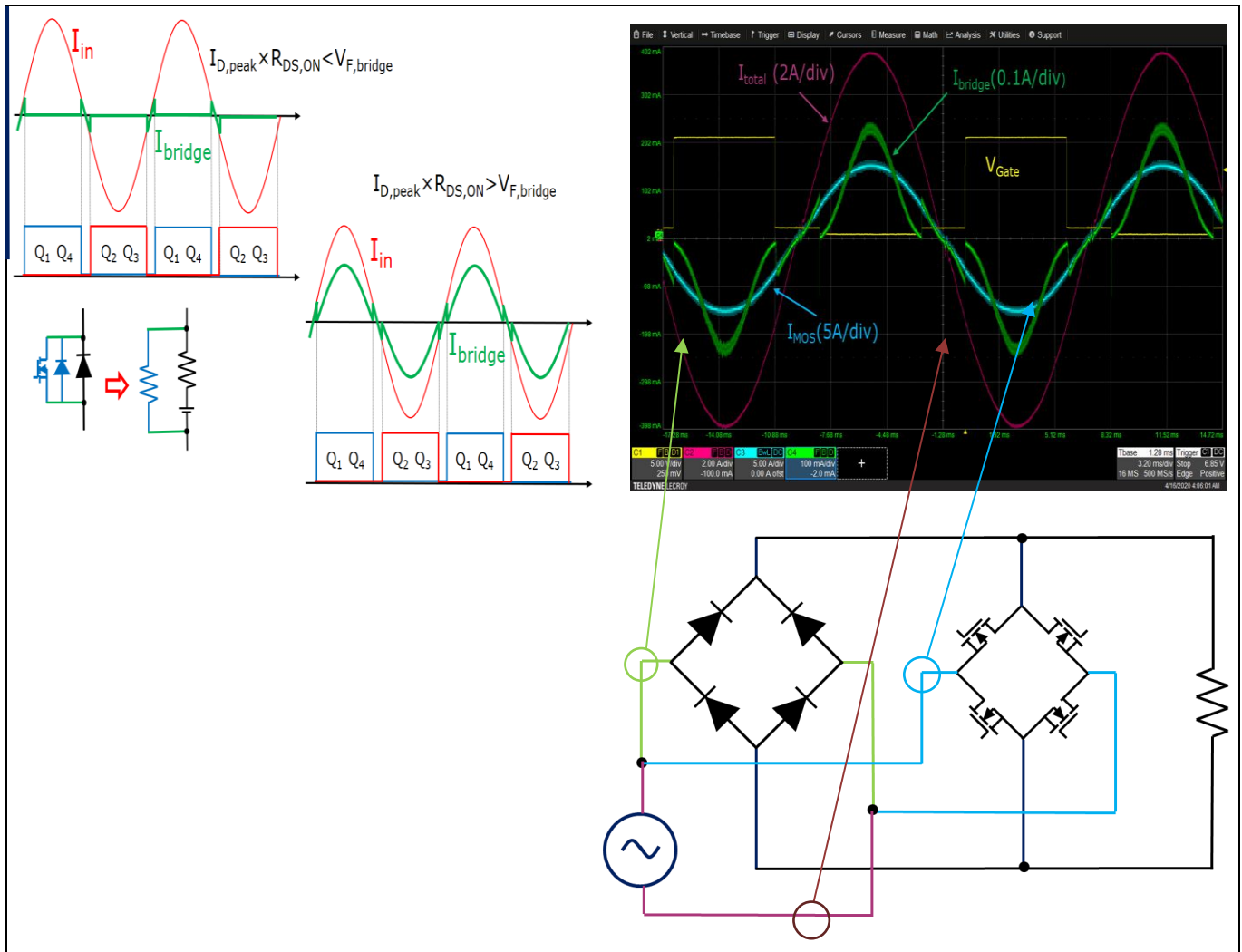


Figure 33 Current sharing between the bridge rectifier and MOSFET

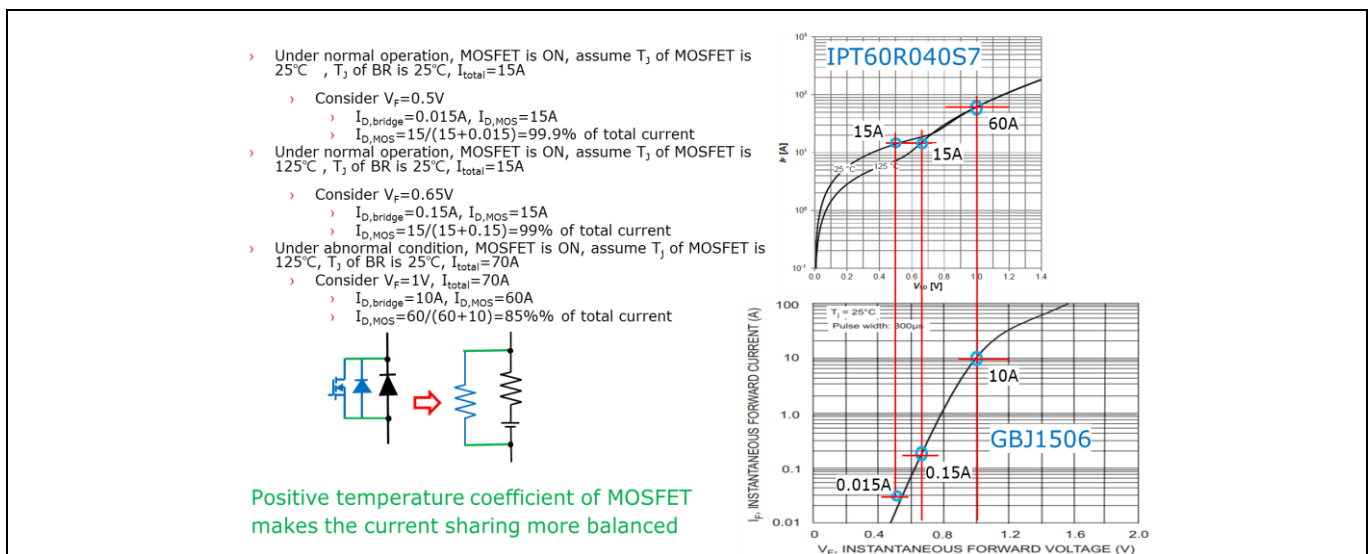


Figure 34 Current sharing between the bridge rectifier and MOSFET at different device temperatures

Surge voltage and surge current solutions for active bridge line rectification

Assuming that the forward voltage of a bridge rectifier is 0.5 V under a total current of 15 A at normal operation, the temperature of the MOSFET is 25°C and the temperature of the bridge rectifier is 25°C, then the current of the MOSFET is 99.9 percent of total current. At the same load condition but the temperature of MOSFET is 125°C and the temperature of the bridge rectifier is 25°C, then the current of the MOSFET is 99 percent of total current.

Assuming in another case that the forward voltage of the bridge rectifier is 1 V with a higher current of 70 A at abnormal condition and the temperature of the MOSFET and bridge rectifier is 125°C and 25°C respectively, then the current of the MOSFET drops to 60 A, which is 85 percent of the total current. From the calculation results, the bridge rectifier does share more current when the MOSFET is at higher current.

Figure 35 shows a total current and current of a bridge rectifier waveform in a 1200 W PFC after an AC cycle drop-out. During normal operation, almost no current flows through the bridge rectifier. With higher currents, the bridge rectifier shares a portion of the total current to prevent active bridge line rectification from being damaged by extremely high currents.

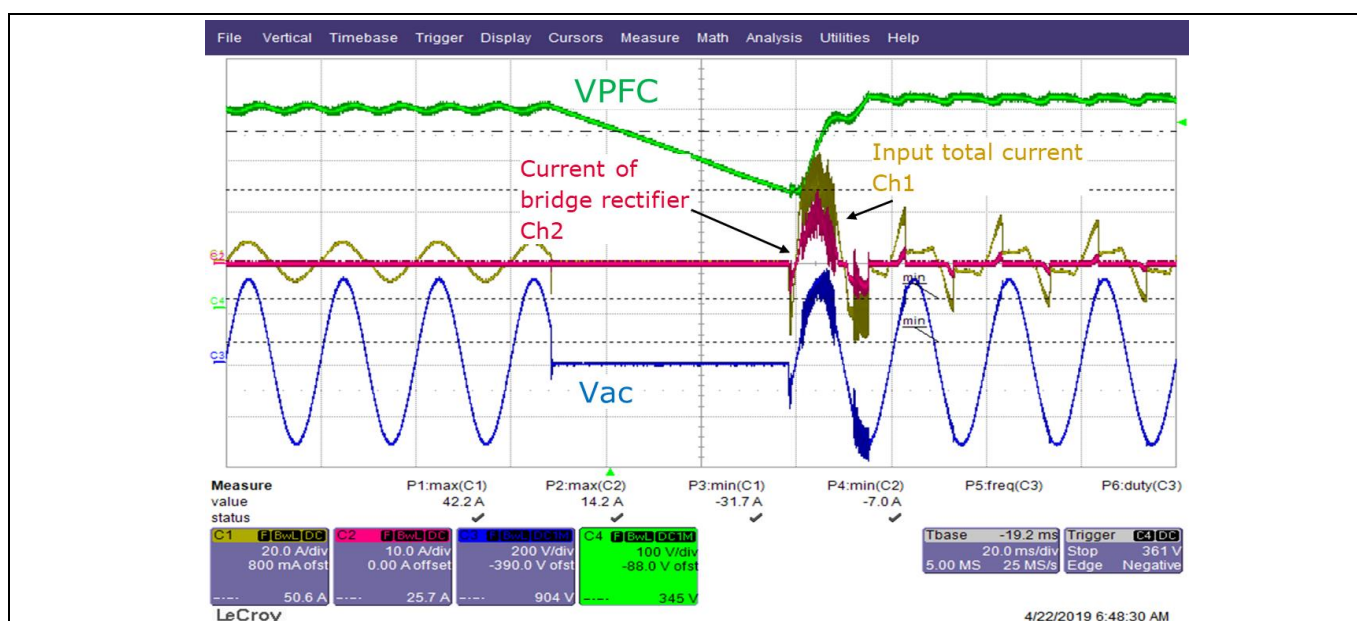


Figure 35 Current sharing by a bridge rectifier after an AC cycle drop-out

Efficiency improvements demonstration with active bridge line rectification

6 Efficiency improvements demonstration with active bridge line rectification

6.1 Active bridge line rectification in a 2400 W single-phase CCM PFC

An active bridge line rectification with a 65 mΩ MOSFET in TOLL package is tested in a 2400 CCM PFC circuit with a 75 kHz switching frequency. At a 230 V AC input and half-load test conditions, the effective input current is around 5.3 A. Assume the forward voltage of the bridge rectifier is around 0.78 V, and the total power dissipation is around 8.26 W. The active bridge line rectification power dissipation is 2.24 W with 80 mΩ of $R_{DS(on)}$ at a 100°C device temperature. The maximum efficiency improvement is around 0.5 percent based on this calculation.

Test results are shown in [Figure 36](#). The efficiency improvement at half load is around 0.42 percent. The efficiency of the PFC board at half load with active bridge line rectification is up to 98.8 percent.

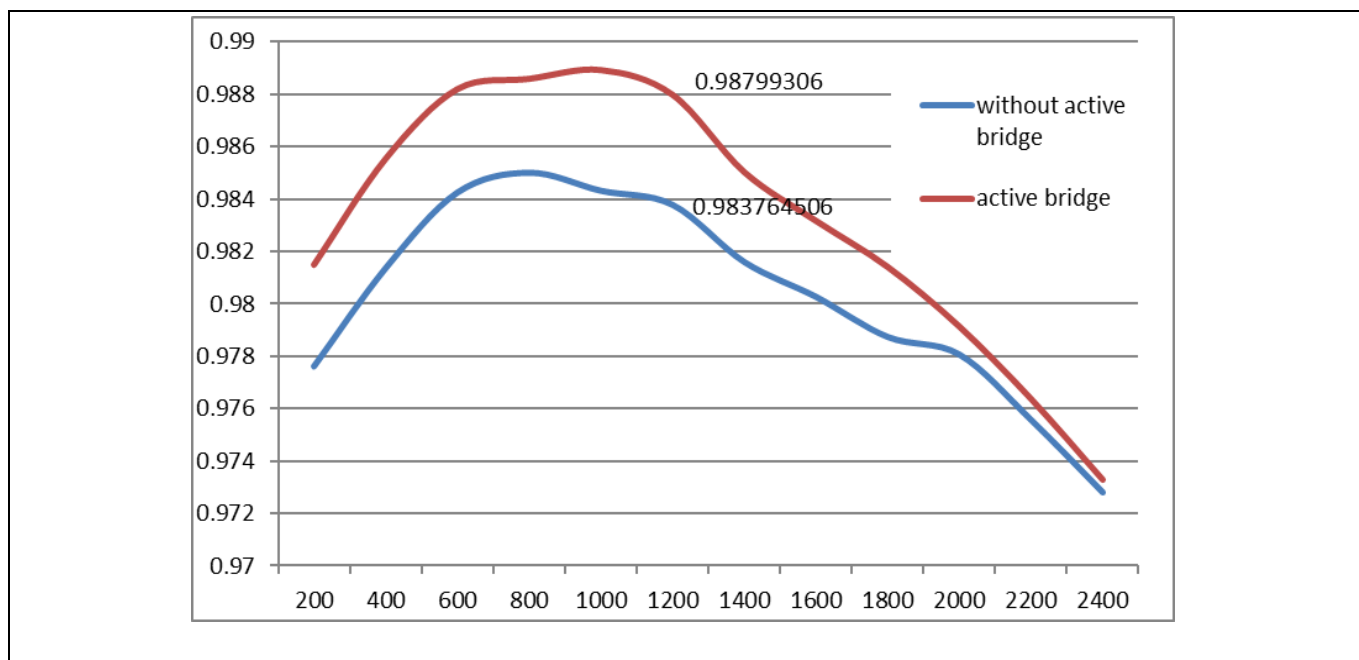


Figure 36 Efficiency improvement of active bridge line rectification in a 2400 W PFC at 230 V AC

6.2 Active bridge line rectification in a 130 W slim-type adapter

Active bridge line rectification with a 65 mΩ MOSFET in ThinPAK package is tested in a 130 W slim-type adapter. Considering the full-load condition at a 90 V AC input voltage, the effective input current is 1.6 A. Assuming the forward voltage of the bridge rectifier is 0.7 V, the power dissipation is around 2.24 W. The MOSFET $R_{DS(on)}$ at 100°C is 100 mΩ, leading to 0.512 W of power dissipation. With the active bridge line rectification, 1.78 W of power dissipation are reduced; that represents a 1.1 percent efficiency improvement caused by the active bridge line rectification. From test results, the efficiency improvement meets the calculation.

Efficiency improvements demonstration with active bridge line rectification

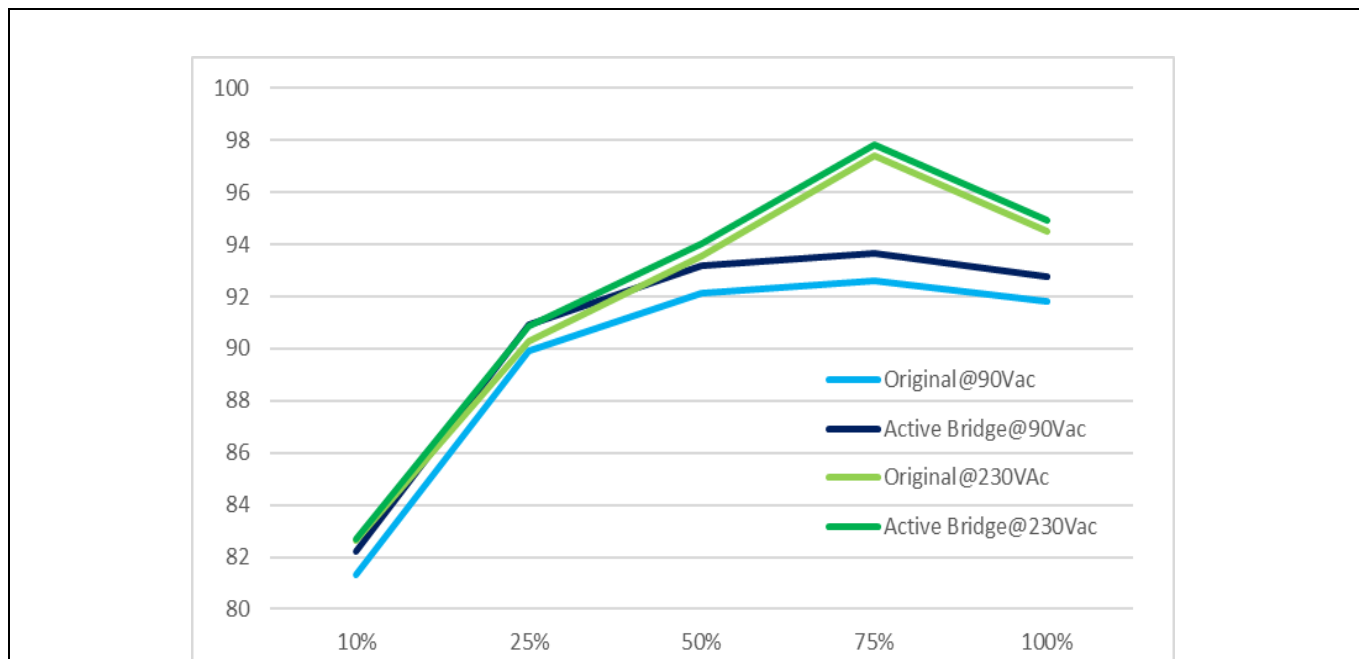


Figure 37 Efficiency test results of active bridge line rectification in a 130 W adapter

6.3 Reference schematic of active bridge line rectification

An active bridge line rectification reference schematic is shown in [Figure 38](#) for readers to build an active bridge line rectification.

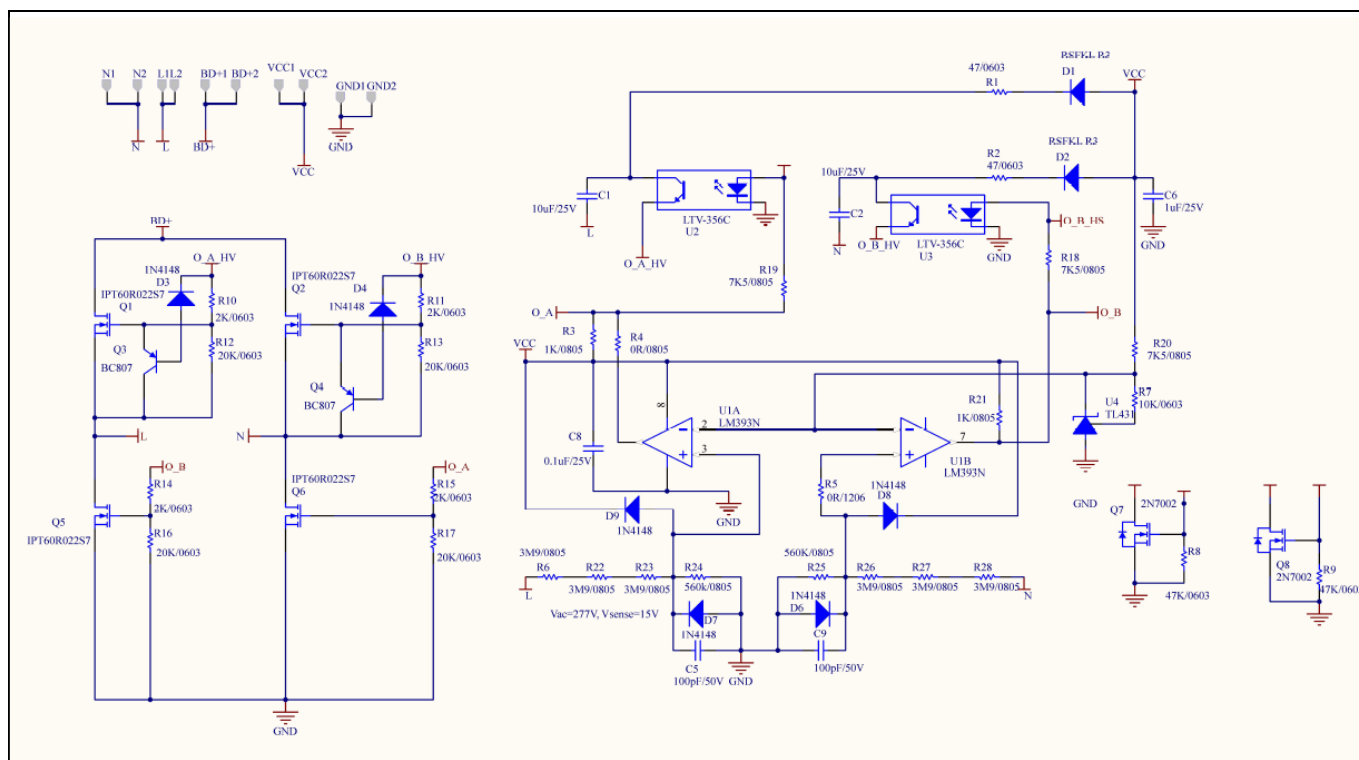


Figure 38 Reference schematic of active bridge line rectification

Summary

7 Summary

Active bridge line rectification is a circuit which can improve the efficiency within entire power ranges for high efficiency and high power density in SMPS. It demonstrates a flexible design with different daughter board MOSFET $R_{DS(on)}$ for various efficiency requirements of different applications without any other circuit modification. For high power density adapters with burst mode control and convection cooling, but without internal auxiliary power, active bridge line rectification does reduce the power loss and temperature of power devices. For server power supplies, active bridge line rectification does help to improve the efficiency and extend the power range with at least 94 percent efficiency. The total power loss reduction and efficiency improvement can be estimated by the simple formulas provided in this application note.

For best performance, the MOSFET $R_{DS(on)}$ plays an important role in this application. Considering the mechanical outline, space and thermal conduction inside power supplies, various MOSFET packages are the key to achieve flexibility for such applications. Infineon provides the lowest MOSFET $R_{DS(on)}$ within the same package and MOSFETs with new top-side cooling SMD packages.

Taking into consideration abnormal conditions and EMC tests, solutions for surge voltage and surge current are necessary for MOSFETs. These are also discussed in this application note. Even when active bridge line rectification acts as a bridge rectifier, a bridge rectifier is still needed, as when they are used in parallel, higher surge current capabilities are possible for abnormal conditions.

Efficiency improvement results with active bridge line rectification are demonstrated in a 2400 W PFC and 130 slim-type adapter. A schematic of a reference circuit is provided in this application note, so that readers can design and manufacture an active bridge line rectification board following the concept.

References

8 References

- [1] Infineon application note, "IR11688 Smart Rectifier™ control IC design notes"
- [2] Diodes datasheet, "GBJ15005-GBJ1510"
- [3] Shindengen datasheet, "D25XB60"

Revision history

Revision history

Document version	Date of release	Description of changes
V 1.0	24-04-2020	First release

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Edition 2020-04-24

Published by

Infineon Technologies AG

81726 Munich, Germany

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Document reference

AN_1905_PL52_1905_101502

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